

L99MM70XP

Integrated microprocessor driven device intended for LIN controlled exterior mirrors

Features

- 5 V low-drop voltage regulator (150 mA max.)
- Embedded LIN transceiver: 2.0/2.1 compliant and SAEJ2602 compatible
- Independent control of mirror adjustment motors
- One full bridge for 3 A load ($R_{on} = 300 \text{ m}\Omega$)
- Two (three) half bridges for 0.5 A load $(R_{on} = 1.6 \Omega)$
- One configurable high-side driver for up to 1.5 A load ($R_{on} = 500 \text{ m}\Omega / 10 \text{ Watt bulb}$ control, or 1600 m Ω / LED control)
- Two high-side driver for 0.5 A load $(R_{on} = 1600 \text{ m}\Omega)$
- One low-side driver 0.5 A load (R_{on} = 1600 mΩ) used as half bridge with highside driver for independent mirror axis control
- One high-side driver for 6 A load $(R_{on} = 90 \text{ m}\Omega)$
- One high-side driver for 0.5 A load (R_{on} = 1600 mΩ) to supply an external MOSFET to drive an EC-glass
- Integrated EC glass control via an external MOSFET with fast discharge path: EC-glass can be discharged to GND or to -1 V
- Programmable soft start function to drive loads with higher inrush currents (>6 A, >1.5 A)
- Very low current consumption modes
- All outputs short-circuit and overtemperature protected
- Two thermal shutdown thresholds and early temperature warning
- Current monitor output for all high-side drivers
- Open-load diagnostic for all outputs
- Overload diagnostic for all outputs
- 3 PWM control signals for all outputs



- Charge pump output for active reverse polarity protection via an external N-channel MOSFET
- STM standard serial peripheral interface for control and diagnosis
- INH input for external CAN transceiver

Applications

LIN controlled mirror

Description

The L99MM70XP is a microcontroller driven multifunctional system ASSP dedicated for LIN controlled wing mirror applications. The device contains a voltage regulator to supply the microcontroller and a LIN2.1 physical layer. Up to 3 DC motors and five grounded resistive loads can independently be driven with four (five) half bridges and five high-side driver. The EC-glass control block provides overvoltage protection with a fast discharge path versus GND and a negative discharge path for future EC-glass characteristics. The integrated ST SPI controls all operation modes (forward, reverse, brake and high-impedance) and provides all the diagnostic information.

Table 1. Device summary

Package	Order codes		
1 ackage	Tube	Tape and reel	
PowerSSO-36	L99MM70XP	L99MM70XPTR	

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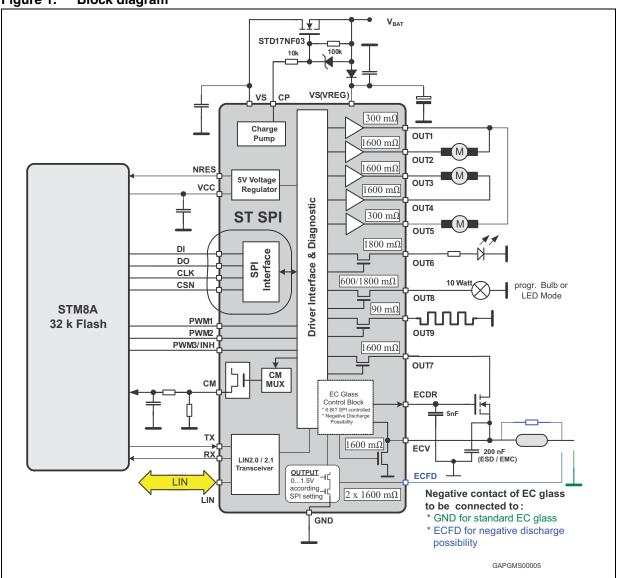
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Block diagram L99MM70XP

1 Block diagram

Figure 1. Block diagram



2 Pin definitions and functions

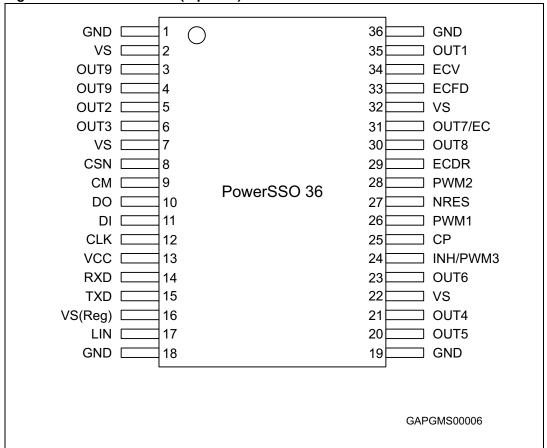
Table 2. Pin definition and functions

Pin	Symbol	Function		
1, 18, 19, 36	GND	Ground: reference potential Note: For the capability of driving the full current at the outputs all pins of GND must be externally connected!		
2, 7, 32	V _S (Power1)	Power supply voltage for outputs OUTX and ECFD (external reverse protection required): for this input a ceramic capacitor as close as possible to GND is recommended.		
22	V _S (Power2)	Note: For the capability of driving the full current at the outputs all pins of V_S must be externally connected! Pins 2, 7 and 32 are internally connected, too. Pin 22 is the power supply for outputs OUT4, 5 and 6.		
3, 4	OUT9	High-side driver output 9: the output is built by a high-side switch and is intended for resistive loads, hence the internal reverse diode from GND to the output is missing.For ESD reason a diode to GND is present but the energy which can be dissipated is limited. The high-side driver is a power DMOS transistor with an internal parasitic reverse diode from the output to V _S (bulk-drain-diode). The output is overcurrent and open-load protected. Note: For the capability of driving the full current at the outputs both pins of OUT9 must be externally connected!		
35, 5, 6, 21, 20	OUT1, OUT2, OUT3, OUT4, OUT5	Half bridge outputs 1,2,3,4,5: the output is built by a high-side and a low-side switch, which are internally connected. The output stage of both switches is a power DMOS transistor. Each driver has an internal parasitic reverse diode (bulk drain diode: high-side driver from output to $V_{\rm S}$, low-side driver from GND to output). This output is overcurrent and openload protected.		
8	CSN	Chip select not input: this input is low active and requires CMOS logic levels. The serial data transfer between the L99MM70XP and the microcontroller is enabled by pulling the input CSN to low-level.		
9	СМ	Current monitor output: depending on the selected multiplexer bits of the control register this output sources an image of the instant current through the corresponding high-side driver with a ratio of 1/10000 or 1/2000.		
10	DO	Serial data output: the diagnosis data is available via the SPI and this 3-state output. The output remains in 3-state, if the chip is not selected by the input CSN (CSN = high).		
11	DI	Serial data input: the input requires CMOS logic levels and receives serial data from the microcontroller. The data is a 24 bit control word and the most significant bit (MSB, bit 23) is transferred first.		
12	CLK	Serial clock input: this input controls the internal shift register of the SPI and requires CMOS logic levels.		
13	VCC	Voltage regulator output: 5 V supply e.g. microcontroller, CAN transceiver.		
14	RXD	Receiver output of the LIN 2.1 transceiver.		
15	TXD	Transmitter input of the LIN 2.1 transceiver		

Table 2. Pin definition and functions (continued)

Pin	Symbol	Function		
16	V _S (Reg)	Power supply voltage (external reverse protection required): for this input a ceramic capacitor as close as possible to GND and an electrolytic capacitor to buffer the voltage during negative transients is recommended.		
17	LIN	LIN bus line		
23	OUT6	High-side driver output 6: The output is built by a high-side switch and is intended for resistive loads; hence the internal reverse diode from GND to the output is missing. For ESD reason a diode to GND is present but the energy which can be dissipated is limited. The high-side driver is a power DMOS transistor with an internal parasitic reverse diode from the output to V_S (bulk-drain-diode). The output is overcurrent and open-load protected.		
24	INH/PWM3	Inhibit input: wake-up from external CAN transceiver. This pin has a second functionality. The microcontroller can use the INH signal to provide a third PWM input for the output OUT8.		
25	СР	Charge pump output: This output is provided to drive the gate of an external n-channel power MOS used for reverse polarity protection (see <i>Figure 1</i>).		
26	PWM1	PWM1 input: This input signal can be used to control the drivers OUT1-OUT5, OUT7, and OUT9 by external PWM signal.		
27	NRES	Low active reset output to the microcontroller: internal pull up of typ. 100k Ω		
28	PWM2	PWM2 input: This input signal can be used to control the driver OUT6 by an external PWM signal.		
29	ECDR	ECDR: using the device in EC control mode this pin is used to control the gate of an external MOSFET.		
30	OUT8	High-side driver output 8: see OUT6 Note: This output can be configured to supply a bulb with low on-resistance or a LED with higher on-resistance in a different application.		
31	OUT7/EC	High-side driver output 7: see OUT6 Note: Beside the bit 8 in control register 2 this output can be switched on setting bit 0 for electrochrome control mode with higher priority.		
33	ECFD	ECFD: using the device in EC control mode this pin is used as "virtual GND" for the EC-glass. For EC-glasses, that require a negative discharge voltage, this supplies the fast discharge voltage. If no EC-glass is used, this pin must be connected to ground.		
34	ECV	ECV: Using the device in EC control mode this pin is used as voltage monitor input. For fast discharge an additional low-side-switch is implemented. This pin can be used as "stand alone" low-side as well. This output is intended for resistive loads only		





3 Description

3.1 Voltage regulator

The L99MM70XP contains a fully protected low drop voltage regulator, which is designed for very fast transient response.

The output voltage is stable with load capacitors > 220 nF.

The voltage regulator provides 5 V supply voltage and up to 100 mA continuous load current for the external digital logic (microcontroller, etc...). In addition the regulator V_{CC} drives the L99MM70XP internal 5 V loads. The voltage regulator is protected against overload and overtemperature. An external reverse current protection has to be provided by the application circuitry to prevent the input capacitor from being discharged by negative transients or low input voltage. The output voltage precision is better than ± 2 % (incl. temperature drift and line-/load regulation) for operating mode; respectively ± 3 % during low current mode. Current limitation of the regulator ensures fast charge of external bypass capacitors. The output voltage is stable for ceramic load capacitors > 220 nF.

If device temperature exceeds TSD1 threshold, all outputs (OUTx, LIN) are deactivated except V_{CC} . Hence the microcontroller has the possibility for interaction or error logging. In case of exceeding TSD2 threshold (TSD2 > TSD1), also V_{CC} is deactivated (see *Figure 8*). A timer is started and the voltage regulator is deactivated for $t_{TSD} = 1$ s.

During this time, all other wake-up sources (LIN) are disabled. After 1 s, the voltage regulator tries to restart automatically. If the restart fails 6 times without clearing and thermal shutdown condition still exists, the L99MM70XP enters the $V_{BAT-standby}$ mode.

In case of short to GND at V_{CC} after initial turn on (V_{CC} < 2 V for at least 4 ms) the L99MM70XP enters the $V_{BAT\text{-standby}}$ mode. Reactivation (wake-up) of the device can be achieved with signals from LIN or INH.

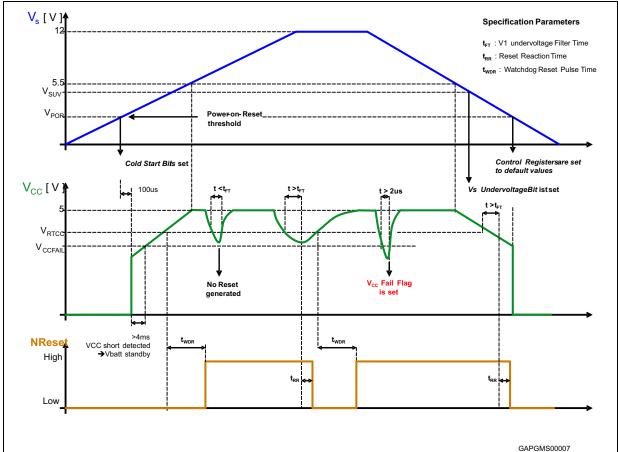


Figure 3. Voltage regulator operation

3.2 Power control in operating modes

The L99MM70XP can be operated in 4 different operating modes:

- Active
- Flash
- V_{CC-standby}
- V_{BAT-standby}

3.2.1 Active mode

All functions are available. After at most 300 µs, the outputs can be enabled.

3.2.2 Flash mode

To disable the watchdog feature a Flash program mode is available. The mode can be entered if the following condition occurs:

 $V_{PWM2} \ge V_{Flash}$

Watchdog is disabled but all other functions are the same as in active mode.

Note: "High" level for flash mode selection is $V_{PWM2} \ge V_{Flash}$. For all other operation modes, standard 5 V logic signals are required.

3.2.3 V_{CC-standby} mode

Outputs and internal loads are switched off. To supply the microcontroller in a low power mode, the voltage regulator (V_{CC}) remains active. The intention of the $V_{CC\text{-standby}}$ mode is to preserve the RAM contents.

A LIN wake-up event sets the device into the active mode and forces the RXD pin to the low-level.

A wake-up over INH switches device in active mode and start the watchdog.

The wake-up via SPI switches device in active mode. A status bit indicates the wake-up source

During the $V_{CC\text{-standby}}$ mode, the current at V_{CC} is monitored.

The transition from active mode to V_{CC-standby} mode is controlled by SPI.

3.2.4 V_{BAT-standby} mode

To achieve minimum current consumption during $V_{BAT\text{-standby}}$ mode, all L99MM70XP functions are switched off.

In $V_{BAT-standbv}$ mode the current consumption of the L99MM70XP is reduced to 8 μ A.

The transition from active mode to V_{BAT-standby} mode is controlled by SPI.

3.3 Wake-up events

A wake-up from standby mode switches the device to active mode. This can be initiated by one or more of the following sources:

- Change of the LIN state at LIN bus interfaces
- SPI access in V_{CC-standby} mode (CSN is low and first rising edge on CLK)
- A current at the INH pin (I > 120 μ A) controlled by the CAN-transceiver (the CAN transceiver is not a part of the IC).

Table 3. Wake-up events

Wake-up source	Description
LIN	Always active
INH	Always active
V _{CC} I _{CMP}	Device remains in $V_{\text{CC-standby}}$ mode with watchdog enabled (If $I_{\text{CMP}} = 0$) and V_{CC} goes into high current mode (increased current consumption). No interrupt is generated.
SPI access	Always active (except in V _{BAT-standby} mode)

LIN wake-up events in $V_{\text{CC-standby}}$ mode generate a low-pulse at RXD for 56 μs .

Wake-up from $V_{\text{CC-standby}}$ by SPI access might be used to check the interrupt service handler.

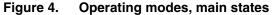
3.4 Functional overview (truth table)

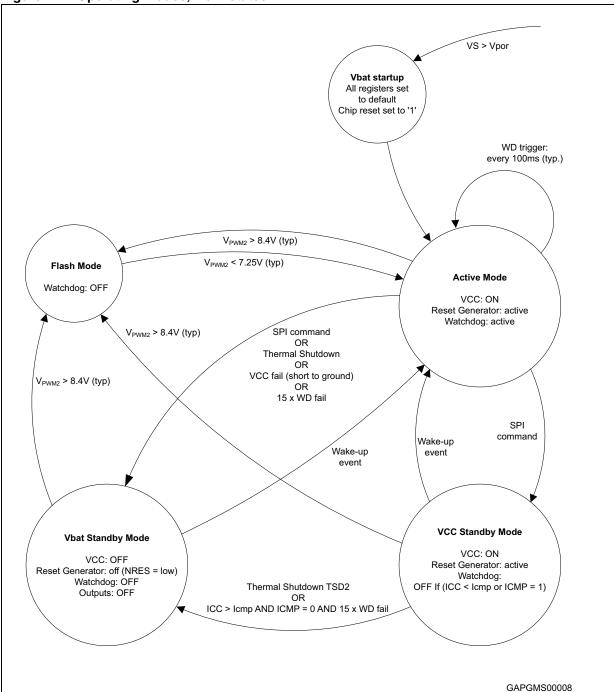
Table 4. Functional overview (truth table)

		Operating modes			
Function	Comments	Active mode	V _{CC-standby} static mode	V _{BAT-standby} static mode	
Voltage regulator, V _{CC}	V _{OUT} = 5 V	On	On ⁽¹⁾	Off	
NRES		On	On	Off	
Window watchdog	V _{CC} monitor	On	Off (ON if $I_{CC} > I_{CMP}$ and $I_{CMP} = 0$)	Off	
LIN	LIN 2.1	On	Off ⁽²⁾	Off ⁽²⁾	

^{1.} Supply the processor in low current mode.

^{2.} The bus state is internally stored when going to standby mode. A change of bus state leads to a wake-up after exceeding of internal filter time.





3.5 Interrupt

In case of $V_{CC\text{-standby}}$ mode and ($I_{CC} > I_{CMPris}$), the device remains in standby mode, the V_{CC} regulator switches to high current mode and the watchdog is started. No interrupt is generated.

If bit NINTEN (CR1/Bit5, default value is set) is set, the RXD pin works also as interrupt output in case of wake-up by LIN or INH or SPI in $V_{\text{CC-standby}}$ mode. This pin is pulled down for 56 μ s.

If it is not set, RXD is pulled down for 56us only for LIN wake-up.

3.6 Time-out watchdog

During normal operation, the watchdog monitors the microcontroller within a 100 ms trigger cycle.

In V_{BAT-standby} and flash program modes, the watchdog circuit is automatically disabled.

After power on or standby mode, the watchdog is started immediately with the normal cycle time (100 ms). The microcontroller has to run its own setup and then to trigger the watchdog via the SPI. The trigger is finally accepted when the CSN input becomes high after the transmission of the SPI word.

Writing '1' to the watchdog trigger bit restarts the watchdog. Subsequently, the microcontroller has to serve the watchdog by alternating the watchdog trigger bit within the safe trigger area (refer to *Figure 10*). A correct watchdog trigger signal immediately starts the next cycle.

If the micro does not serve the watchdog in time, the watchdog pulls low the NRES output for 2 ms. At the same time, the watchdog failure counter (WDFAIL) is incremented by 1 and the device enters passive mode.

After 8 watchdog failures in sequence, the V_{CC} regulator is switched off for 200 ms. If subsequently, 7 additional watchdog failures occur, the V_{CC} regulator is completely turned off and the device goes into $V_{BAT\text{-standby}}$ mode until a wake-up occurs.

In case of a watchdog failure, the outputs (OUTx) are switched off and the device enters passive mode (i.e. all control registers are set to default values).

Vbat standby mode (8+7)x WD failures Wake-up event VCC off for 200ms 200 ms 8x WD failure Watchdog failure (No trigger) Reset Invert trigger bit Watchdog active (NRES low for before end of 2ms) watchdog time After 2 ms Poweron Reset Wake-up event from VCC standby or flash mode Watchdog inactive: Vbat standby Wake-up event VCC standby from Vbat standby Flash mode Go to standby or flash mode GAPGMS00009

Figure 5. Watchdog state diagram

3.7 Passive mode

L99MM70XP enters passive mode in case of:

- Watchdog failure
- V_{CC} under voltage (NRES)
- Thermal shutdown TSD2
- SPI data in stuck at 0 or 1

In passive mode all control registers (except the reset level bit RSTLVL) and the configuration register are set to default so that all outputs are switched off. The PASSIVE bit inside the global status byte is set to "1". The first valid SPI frame after entering the passive mode resets the PASSIVE bit to "0" and leaves passive.

3.8 Reset output (NRES)

If V_{CC} is turned on and the voltage exceeds the V_{CC} reset threshold, the reset output NRES is pulled up by internal pull up resistor to V_{CC} voltage after a 2 ms reset delay time. This is necessary for a defined start of the microcontroller when the application is switched on.

A low active reset pulse (2 ms) is generated in case of:

- V_{CC} drops below V_{rth} (configurable by SPI) for more than 8 μs (V_{CC} under voltage)
- Watchdog failure

If NRES is pulled low, all control registers (except the reset level bit RSTLVL) and the configuration register are set to default. In both cases, the device enters passive mode.

3.9 V_{CC} fail

The V_{CC} regulator output voltage is monitored.

In case of a drop below the V_{CC} fail threshold (V_{CC} < 2 V typ. for t > 2 μ s), the V_{CC} fail bit is latched. The fail bit is cleared by a dedicated SPI command.

If 4 ms after turn on of the regulator the V_{CC} voltage is below the V_{CC} fail threshold, the L99MM70XP identifies a short circuit condition at the regulator output and switch it off.

In case of V_{CC} short to GND failure the device enters V_{BAT-standby} mode automatically.

3.10 Output drivers OUT1 ... OUT9

3.10.1 Load condition

Each half bridge is built by internally connected high-side and low-side power DMOS transistors. Due to the built-in reverse diodes of the output transistors, inductive loads can be driven at the outputs OUT1 to OUT5 without external free-wheeling diodes. The drivers OUT6, OUT7, OUT8, OUT9, ECV and ECFD are intended to drive resistive loads. Therefore only a limited energy (E < 1 mJ) can be dissipated by the internal ESD-diodes in freewheeling condition. For inductive loads (L > 100 μ H) an external free wheeling diode connected between GND and the corresponding output is required.

3.10.2 Current monitor

The current monitor output sources a current image at the current monitor output, which has two fixed ratios of the instantaneous current of the selected high-side driver. Outputs with a resistance of 500 m Ω and higher have a ratio of 1/2000 and those with a lower resistance of 1/10000. The signal at output CM is blanked after switching on the driver until correct settlement of the circuitry (at least for 32 μ s). The bits 0 to 3 of the control register 3 define which of the outputs are multiplexed to the current monitor output CM. The current monitor output allows a more precise analysis of the actual state of the load rather than the detection of an open-load or overload condition. For example, it can be used to detect the motor state (starting, free running, stalled). Moreover, it is possible to control the power of the defroster more precisely by measuring the load current.

3.10.3 PWM inputs

Each driver has a corresponding PWM enable bit, which can be programmed by the SPI interface. If the PWM enable bit is set in control register 2 or 3, the output is controlled by the logically AND-combination of the PWM signal and the output control bit in control register 0 or 1. The outputs OUT1-5, 7, 9, ECV are controlled by the PWM1 input, the output OUT6 is controlled by the input PMW2 and output OUT8 is controlled by INH/PWM3. Thus, the three PWM inputs can be used to dim three lamps independently by external PWM signals.

Switching off the outputs, a delay of maximum 300 μ s is introduced (see also *Table 18* in *Section 8.9.2: Switching times*), hence the off time of the PWM input signal should be at least 300 μ s.

3.10.4 Cross current protection

The half bridges of the device are cross current protected by an internal delay time. If one driver (LS or HS) is turned off, the activation of the other driver of the same half bridge is automatically delayed by the cross current protection time. After the cross current protection time is expired, the slew-rate limited switch off phase of the driver is changed to a fast turn-off phase and the opposite driver is turned on with slew-rate limitation. Due to this behavior, it is always guaranteed that the previously activated driver is completely turned off before the opposite driver starts to conduct.

3.10.5 Programmable soft start function

Loads with startup currents higher than the overcurrent limits (e.g. inrush current of lamps, start current of motors and cold resistance of heaters) can be driven by using the programmable soft start function (i.e. overcurrent recovery mode). Each driver has a corresponding overcurrent recovery bit. If this bit is set, the device automatically switches the outputs on again after a programmable recovery time. The duty cycle in overcurrent condition can be programmed by the SPI interface to about 12 % or 25 %. The PWM modulated current provides sufficient average current to power-up the load (e.g. heat up the bulb) until the load reaches operating condition. The PWM frequency settles at 1.7 kHz and 3 kHz.

The device itself cannot distinguish between a real overload and a non-linear load like a light bulb. A real overload condition can only be qualified by time. As an example, the microcontroller can switch on the light bulbs by setting the overcurrent recovery bit for the first 50 ms. After clearing the recovery bit, the output is automatically switched off, if the overload condition remains.

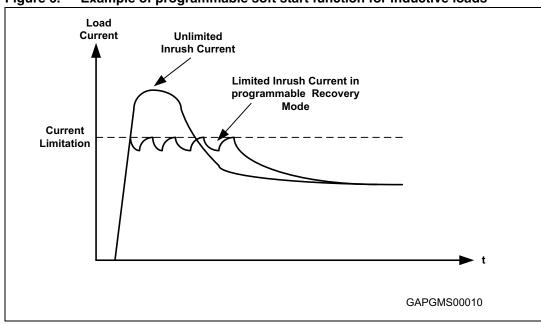


Figure 6. Example of programmable soft start function for inductive loads

3.11 Controller for electrochromic glass

The voltage of an electrochromic element connected at pin ECV can be controlled to a target value, which is set by the bits EC<5:0> (Control register 2, bits 6 down to 1). Setting bit ECON (control register 2, bit 0) enables this function. An on-chip differential amplifier and an external MOS source follower, with its gate connected to pin ECDR, and which drives the electrochrome mirror voltage at pin ECV, form the control loop. The drain of the external MOS transistor is supplied by OUT7. A diode from pin ECV (anode) to pin ECDR (cathode) has been placed on the chip to protect the external MOS source follower. A capacitor of at least 5 nF has to be added to pin ECDR for loop-stability. The target voltage is binary coded with a full-scale range of 1.5 V. If bit ECVL (control register 3, bit 5) is set to '1', the maximum controller output voltage is clamped to 1.2 V without changing the resolution of bits EC<5:0>. When programming the ECVLS driver to on-state, the voltage at pin ECV is pulled to ground by a 1.6 Ohm low-side switch until the voltage at pin ECV is less than dV_{ECVhi} higher than the target voltage (fast discharge).

The status of the voltage control loop is reported via SPI. Bit ECVO (status register 3, bit 4) is set, if the voltage at pin ECV is higher, whereas bit ECVNR (status register 3, bit 5) is set, if the voltage at pin ECV is lower than the target value. Both status bits are valid, if the voltage is stable for at least the ECVO/ECVNR filter time and are not latched.

Since OUT7 is the output of a high-side driver, it contains the same diagnose functions as the other high-side drivers (e.g. during an overcurrent detection, the control loop is switched off). In electrochrome mode, OUT10 cannot be controlled by PWM mode. For EMS reasons the loop capacitor at pin ECDR as well as the capacitor between ECV and GND have to be placed to the respective pins as close as possible (see *Figure 13* for details).

If the electrochrome element is connected between the pins ECV and ECFD instead between ECV and ground, a negative voltage can be applied to the device by pulling ECFD to a higher value than ECV, which is connected to ground by a 1.6 Ohm low-side switch. In this mode the voltage at pin ECFD is controlled to the target value defined by the register EC<5:0>. This is done using an on-chip source-follower transistor (see *Figure 14* for details). The negative discharge is enabled by setting bit ECND (control register 2, bit 7) to '1'.

During normal (positive) voltage control the low-side driver at pin ECFD must be switched on to connect the electrochrome element to ground.

Pin ECDR is pulled resistively (R_{ECDRDIS}) to ground while not in electrochrome mode.

3.12 LIN bus interface

3.12.1 General features

- Speed communication up to 20 kbit/s
- High speed Flash mode 100 kbit/s
- LIN 2.1 compliant (SAEJ2602 compatible) transceiver
- Function range from +40 V to -18 V DC at LIN pin
- GND disconnection fail safe at module level
- Off mode: does not disturb network
- GND shift operation at system level
- Microcontroller Interface with CMOS compatible I/O pins
- Pull up internal resistor
- ESD: immunity against automotive transients per ISO7637 specification
- Matched output slopes and propagation delay

In order to further reduce the current consumption in standby mode, the integrated LIN bus interface offers an ultra low current consumption.

3.12.2 LIN error handling

The L99MM70XP provides the following 3 error handling features which are not described in the LIN Specifications V2.1, but are realized in different stand alone LIN transceivers/microcontrollers to switch the application back to normal operation mode.

Dominant TXD time out

A permanent low-level on pin TXD would force the bus into a permanent dominant state, blocking all network communication. If pin TXD remains at low-level for longer than the TXD dominant timeout $t_{dom(TXD)}$, the transmitter is disabled. The status bit is latched and can be read and optionally cleared by SPI. The transmitter remains disabled until the status register is cleared. This feature can be disabled via SPI.

LIN BUS permanent recessive

If TXD changes to low-level but the bus does not follow within $t_{rec(LIN)}$, the transmitter is disabled. The status bit is latched and can be read and optionally cleared by SPI. The transmitter remains disabled until the status register is cleared.

LIN BUS permanent dominant

If a dominant state on the bus persists for longer than $t_{dom(LIN)}$ a permanent dominant status is detected. The status bit is latched and can be read and optionally cleared by SPI. The transmitter of the transceiver is not disabled.

Note:

A wake-up caused by a message on the bus starts the voltage regulator and the microcontroller to switch the application back to normal operation mode.

3.12.3 Wake-up (from LIN bus)

In standby mode the L99MM70XP can receive a wake-up from LIN bus. For the wake-up feature the L99MM70XP logic differentiates two different conditions.

Normal wake-up

Normal wake-up can occur when the L99MM70XP was set in standby mode while a recessive (state was present on the bus. A dominant level at LIN for $t > t_{linbus}$, switches the L99MM70XP to active mode. An interrupt is generated at the RXD/NINT pin.

Wake-up from short to GND condition

If the L99MM70XP was set in standby mode while LIN was in dominant (low) state, recessive level at LIN for t_{linbus} , switches the L99MM70XP to active mode. An interrupt is generated at the RXD/NINT pin.

3.13 Serial peripheral interface (ST SPI standard)

A 24 bit ST-SPI is used for bi-directional communication with the microcontroller.

During active mode, the SPI

- Triggers the watchdog
- Controls the modes and status of all L99MM70XP modules (incl. input and output drivers)
- Provides driver output diagnostic
- Provides L99MM70XP diagnostic (incl. overtemperature warning, L99MM70XP operation status)

Note: During standby modes, the SPI is generally deactivated.

The SPI can be driven by a microcontroller with its SPI peripheral running in following mode:

CPOL = 0 and CPHA = 0.

For this mode, input data is sampled by the low to high transition of the clock CLK, and output data is changed from the high to low transition of CLK.

This device is not limited to microcontroller with a build-in SPI. Only three CMOS-compatible output pins and one input pin are needed to communicate with the device. A fault condition can be detected by setting CSN to low. If CSN = 0, the DO pin reflects the global error flag (fault condition) of the device (see *Figure 7*). This operation does not cause the communication error bit in the global status byte to be set.

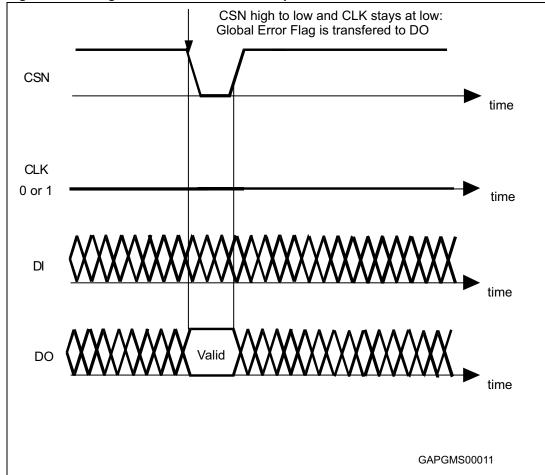


Figure 7. SPI global error information output

Chip Select Not (CSN)

The input pin is used to select the serial interface of this device. When CSN is high, the output pin (DO) is in high impedance state. A low signal activates the output driver and a serial communication can be started. The state during CSN = 0 is called a communication frame.

Serial Data In (DI)

The input pin is used to transfer data serially into the device. The data applied to the DI are sampled at the rising edge of the CLK signal and shifted into an internal 24 bit shift register. At the rising edge of the CSN signal the contents of the shift register is transferred to data input register. The writing to the selected data input register is only enabled if exactly 24 bits are transmitted within one communication frame (i.e. CSN low). If more or less clock pulses are counted within one frame the complete frame is ignored. This safety function is implemented to avoid an activation of the output stages by a wrong communication frame.

Note:

Due to this safety functionality a daisy chaining of SPI is not possible. Instead, a parallel operation of the SPI bus by controlling the CSN signal of the connected IC's is recommended.

Serial Data Out (DO)

The data output driver is activated by a logical low-level at the CSN input and goes from high impedance to a low or high-level depending on the global error flag (fault condition). The first rising edge of the CLK input after a high to low transition of the CSN pin transfers the content of the selected status register into the data out shift register. Each subsequent falling edge of the CLK shifts out the next bit.

Serial Clock (CLK)

The CLK input is used to synchronize the input and output serial bit streams. The Data Input (DI) is sampled at the rising edge of the CLK and the Data Output (DO) changes with the falling edge of the CLK signal.

4 Protection and diagnosis

4.1 Power supply fail

Overvoltage and undervoltage detection on V_S (Power1).

4.1.1 Overvoltage

If the supply voltage V_S rises above the overvoltage threshold (V_{SOV}) for more than 56 μs (typ.)

- The outputs OUT1-9, ECV, ECFD and LIN are switched to high impedance state (load protection). Electrochrome mode is switched off. If the bit OVUVR is set to 0, the outputs are re-enabled automatically if the overvoltage condition is removed. If it is set to 1, then the overvoltage bit has to be cleared to re-enable the outputs. LIN is always automatically re-enabled.
- The overvoltage bit is set and can be cleared with a "read and clear" command.

4.1.2 Undervoltage

If the supply voltage V_S drops below the under voltage threshold voltage (V_{SUV}) for more than 56 μs (typ.)

- The outputs OUT1-9, ECV, ECFD and LIN are switched to high impedance state. Electrochrome mode is switched off. If the bit OVUVR is set to 0, the outputs are reenabled automatically if the under voltage condition is removed. If it is set to 1, then the under voltage bit has to be cleared to re-enable the outputs. LIN is always automatically re-enabled.
- The under voltage bit is set and can be cleared with the "read and clear" command.

4.2 Diagnosis functions

Digital diagnosis features are provided by SPI:

- V_{CC} reset (threshold programmable)
- Overtemperature including pre warning
- Open-load status separately for each output OUT1-9, ECV, ECFD
- Overload status separately for each output OUT1-9, ECV, ECFD
- V_{S-supply} overvoltage undervoltage
- V_{CC} fail bit
- Chip reset bit (start from power-on reset)
- Number of unsuccessful V_{CC} restarts after thermal shutdown
- Number of sequential watchdog failures
- LIN diagnosis (permanent recessive/dominant, dominant TXD)
- Device state (wake-up from V_{CC-standby} or V_{BAT-standby})
- Forced V_{BAT-standby} after WD-fail, forced V_{BAT-standby} after overtemperature
- Watchdog timer state (diagnosis of watchdog)
- Passive mode
- SPI communication error

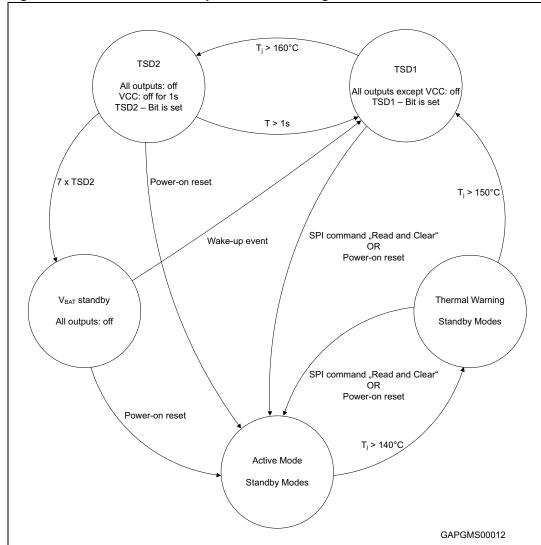


Figure 8. Thermal shutdown protection and diagnosis

4.3 Temperature warning and thermal shutdown

See Figure 8.

4.4 Half bridge outputs

The device provides a total of 5 half bridge outputs OUT1,2,3,4,5 to drive inductive loads (e.g. motor).

The half bridges are protected against

- Overvoltage and undervoltage
- Overload (short circuit)
- Overtemperature with pre warning

If the output current exceeds the current shutdown threshold the output transistor is turned off and the corresponding diagnosis bit of the output is latched. The status can be read and cleared from SPI. If the overcurrent recovery mode is set for this output, the output is switched on again in order to provide a soft start function (see *Section 3.10.5: Programmable soft start function*) and the status bit is cleared automatically. Otherwise the output stays off until the status bit is cleared.

The outputs are automatically switched off in case of passive mode, V_S undervoltage, V_S overvoltage, thermal shutdown (TSD1 and TSD2) or stuck at 1/0 condition at DI.

4.5 High-side driver outputs

The device provides a total of 4 high-side outputs OUT6,7,8,9 to drive LED or defroster.

The high-side outputs are protected against

- Overvoltage and undervoltage (can be masked by SPI)
- Overload (short circuit)
- Overtemperature with pre warning

If the output current exceeds the current shutdown threshold the output transistor is turned off and the corresponding diagnosis bit of the output is latched. The status can be read and cleared from SPI. If the overcurrent recovery mode is set for this output, the output is switched on again in order to provide a soft start function (see *Section 3.10.5: Programmable soft start function*) and the status bit is cleared automatically. Otherwise the output stays off until the status bit is cleared.

The outputs are automatically switched off in case of passive mode, V_S undervoltage, V_S overvoltage, thermal shutdown (TSD1 and TSD2) or stuck at 1/0 condition at DI.

Note:

Loss of ground or ground shift with externally grounded loads: ESD structures are configured for nominal currents only. If external loads are connected to different grounds, the current load must be limited to this nominal current.

5 Absolute maximum ratings

Table 5. Absolute maximum ratings

Symbol	Parameter/test condition	Value [DC voltage]	Unit	
V _S	DC supply voltage/jump start	-0.3 to +28	V	
	Load dump		-0.3 to +40	٧
V	Stabilized aupply voltage legic cupply	V _S < 5.2 V	-0.3 to V _S + 0.3	V
V _{CC}	Stabilized supply voltage, logic supply	V _S > 5.2 V	-0.3 to 5.5	V
V _{DI} , V _{CLK} , V _{TXD} , V _{CSN} , V _{DO} , V _{RXD} , V _{NRES} , V _{CM} , V _{PWM1}	Logic input/output voltage range	Logic input/output voltage range		V
V _{PWM2} , V _{PWM3}	Logic input voltage		-0.3 to V _S + 0.3	٧
V _{CP}	Charge pump output		-25 to 39	V
V _{OUTn,ECDR,ECV,} ECFD	Static output voltage (n = 1 to 9)		-0.3 to V _S + 0.3	V
I _{OUT2,3,4,6,7,ECV,} ECFD [,] I _V S(REG)	Output current ⁽¹⁾		±1.25	Α
I _{OUT1,5,8,9} , I _{VS(Power)} ,I _{GND}	Output current ⁽¹⁾		±5	Α
I _{Pin to Pin}	Maximum output current between pin 2 and 32 or 7 and 32 ⁽¹⁾		±1	Α
V _{LIN}	LIN bus I/O voltage range	-20 to +40	V	

Values for the absolute maximum current through bond wire. It doesn't consider maximum power dissipation or other limits.

Note:

All maximum ratings are absolute ratings. Exceeding the limitation of any of these values may cause an irreversible damage of the integrated circuit!

L99MM70XP ESD protection

6 ESD protection

Table 6. ESD protection

Parameter	Value	Unit
All pins ⁽¹⁾	±2	kV
All output pins ⁽²⁾ (OUT1-OUT9, ECV, ECFD)	±4	kV
LIN ⁽²⁾	±8 ⁽³⁾	kV
All pins (charge device model) ⁽⁴⁾	±500	V
Corner pins (charge device model) ⁽⁴⁾	±750	V

^{1.} HBM (human body model, 100 pF, 1.5 k Ω) according to MIL 883C, Method 3015.7 or EIA/JESD22A114-A.

For detailed information please see EMC report from IBEE Zwickau (available on request).

^{2.} HBM with all unzapped pins grounded.

^{3.} With external components.

^{4.} According charged device model: JEDEC JESD22-C101D.

Thermal data L99MM70XP

7 Thermal data

Table 7. Operating junction temperature

Symbol	Parameter		
Tj	Operating junction temperature	-40 to 150	°C

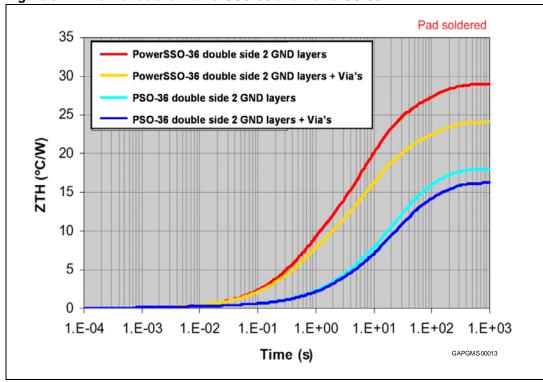
Note: R_{thjA}, typical value, without PCB.

Table 8. Temperature warning and thermal shutdown

Symbol	Parameter		Min.	Тур.	Max.	Unit
T _{W ON}	Thermal overtemperature warning threshold	T _j ⁽¹⁾	130	140	150	°C
T _{SD1 OFF}	Thermal shutdown junction temperature 1	T _j ⁽¹⁾	140	150	160	°C
T _{SD2 OFF}	Thermal shutdown junction temperature 2	T _j ⁽¹⁾	150	160	170	°C

^{1.} Non-overlapping.

Figure 9. Thermal data of PowerSSO-36 and PowerSO-36



8 Electrical characteristics

8.1 Supply and supply monitoring

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq VS \leq 18 V; all outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 9. Supply and supply monitoring

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V _{SUV ON}	V _S undervoltage threshold voltage	V _S increasing	5.7		7.2	V
V _{SUV OFF}	V _S undervoltage threshold voltage	V _S decreasing	5.5		6.9	V
V _{SUV hyst}	V _S undervoltage hysteresis	V _{SUV ON} - V _{SUV OFF}		0.5		V
V _{SOV OFF}	V _S overvoltage threshold voltage	V _S increasing	18.1		24.5	V
V _{SOV ON}	V _S overvoltage threshold voltage	V _S decreasing	17.5		23.5	V
V _{SOV hyst}	V _S overvoltage hysteresis	V _{SOV OFF} - V _{SOV ON}		1		V
I _{VS(act)}	Current consumption in active mode	$V_S = 13.5 \text{ V, TXD LIN high}^{(1)(2)}$		7	20	mA
I _{VSREG(act)}	Current consumption in active mode	$V_{SREG} = 13.5 \text{ V, TXD LIN high}$ $I_{VCC} = 0^{(2)}$		6	12	mA
I _{VS(BAT)}	Current consumption in V _{BAT-standby} mode	$V_S = 13.5 V^{(1)(2)}$		1		μA
I _{VS(BAT)}	Current consumption in V _{BAT-standby} mode	$V_S = 13.5 V^{(1)(3)}$		2		μΑ
I _{VSREG(BAT)}	Current consumption in V _{BAT-standby} mode	V _{SREG} = 13.5 V ⁽²⁾	1	8	16	μΑ
I _{VSREG(BAT)}	Current consumption in V _{BAT-standby} mode	V _{SREG} = 13.5 V ⁽³⁾	2	12	24	μΑ
I _{VS(VBAT)} wupend	Current consumption in V _{BAT-standby} mode with a pending wake-up request	V _S , V _{SREG} = 13.5 V, 2 V < LIN < V _S - 3.5 V		800	1200	μΑ
I _{VS(VCC)} wupend	Current consumption in V _{CC-standby} mode with a pending wake-up request	V _S , V _{SREG} = 13.5 V, 2 V < LIN < V _S - 3.5 V		800	1200	μΑ
I _{VS(VCC)}	Current consumption in V _{CC-standby} mode	V_S = 13.5 V, voltage regulator V_{CC} active, no wake-up request		1		μA
I _{VSREG(VCC)}	Current consumption in V _{CC-standby} mode	$V_S = 13.5$ V, voltage regulator V_{CC} active, no wake-up request, $I_{VCC} = 0^{(2)}$	10	45	70	μΑ
I _{VSREG(VCC)}	Current consumption in V _{CC-standby} mode	$V_S = 13.5 \text{ V, voltage regulator } V_{CC}$ active, no wake-up request, $I_{VCC} = 0^{(3)}$	15	67	105	μΑ

^{1.} OUT1 - OUT9, ECDR ECV, ECFD floating.

^{2.} $T_{Test} = -40 \,^{\circ}\text{C}$, 25 $^{\circ}\text{C}$.

^{3.} $T_{Test} = 85$ °C. This parameter is guaranteed by design.

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8.2 Oscillator

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 4.5 V \leq V_S \leq 28 V; all outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 10. Oscillator

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
f _{CLK}	Oscillation frequency		1.6	2.0	2.70	MHz

8.3 Power-on reset (V_{SREG})

All outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified (see *Figure 3*).

Table 11. Power-on reset (V_{SREG})

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V	V throohold	V _{SREG} increasing	2.8	3.8	4.5	V
V _{POR}	V _{POR} threshold	V _{SREG} decreasing		3.2		V

8.4 Voltage regulator V_{CC}

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq V_{SREG} \leq 28 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 12. Voltage regulator V_{CC}

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V _{CC}	Output voltage			5.0		٧
V _{CC}	Output voltage tolerance active mode	I _{LOAD} = 6 mA50 mA, V _{SREG} = 13.5 V			±2	%
V _{hc}	Output voltage tolerance active mode, high current	I _{LOAD} = 50 mA100 mA, V _{SREG} = 13.5 V			±2.5	%
V _{STB}	Output voltage tolerance V _{CC-standby} mode	$I_{LOAD} = 0 \mu A6 mA,$ $V_{SREG} = 13.5 V$	-2.5		3.5	%
V	Drop out voltage	$I_{LOAD} = 50 \text{ mA}, V_{SREG} = 4.5 \text{ V}$		0.2	0.4	٧
V_{DP}	Drop-out voltage	I _{LOAD} = 100 mA, V _{SREG} = 4.5 V		0.3	0.5	٧
I _{CC}	Output current in active mode	Max. continuous load current			100	mA
I _{CCmax}	Short circuit output current	Current limitation	400	600	950	mA
Cload1	Load capacitor1	Ceramic	0.22			μF
t _{TSD}	V _{CC} deactivation time after thermal shutdown			1		S
I _{CMPris}	Current consumption rising threshold	Rising current (deactivated current monitor)	1.6	3.2	5.2	mA

Table 12. Voltage regulator V_{CC} (continued)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
I _{CMPfal}	Current consumption falling threshold	Falling current (deactivated current monitor)	1.3	2.7		mA
I _{CMPhys}	Current consumption hysteresis			0.5		mA
V _{CCfail}	V _{CC} fail threshold	V _{CC} forced		2		V

8.5 Reset output (V_{CC} supervision)

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 4 V \leq V_S \leq 28 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 13. Reset output (V_{CC} supervision)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
.,		V_{VCC} increasing CR1/Bit4 = $0^{(1)}$	4.6	4.7	4.85	V
V _{RT1}	Reset threshold voltage1	V _{VCC} decreasing CR1/Bit4 = 0	4.5	4.6	4.7	V
V _{RT1HYST}	Threshold voltage 1 hysteresis			0.1		V
V	Reset threshold voltage2	V _{VCC} increasing CR1/Bit4 = 1 ⁽¹⁾	3.6	3.7	3.9	V
V _{RT2}		V _{VCC} decreasing CR1/Bit4 = 1	3.0	3.3	3.5	V
V _{RT2HYST}	Threshold voltage 2 hysteresis			0.4		V
V _{NRES}	Reset Pin low output voltage	V _{CC} > 1 V, I _{NRES} = 1 mA		0.2	0.4	V
R _{NRES}	Reset pull up int. resistor	V _{NRES} = 4 V	60	110	204	kΩ
t _{RR}	Reset reaction time	C _{NRES} = 100 pF, I _{NRES} = 1 mA			40	μs

^{1.} Delay time see t_{WDR} below (Section 8.6: Watchdog).

8.6 Watchdog

4.5 V \leq V_S \leq 28 V; T_{amb} = -40 °C...125 °C, unless otherwise specified, see *Figure 10* and *Figure 11*.

Table 14. Watchdog

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _{LW}	Watchdog cycle time		100	134	180	ms
t _{WDR}	Watchdog reset pulse time		1.5	2.3	2.9	ms

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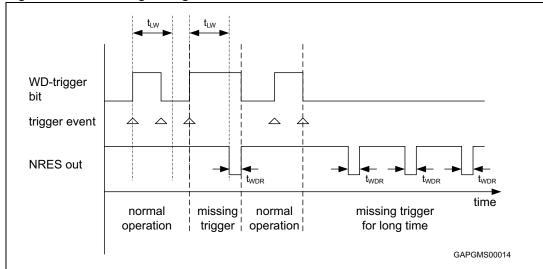
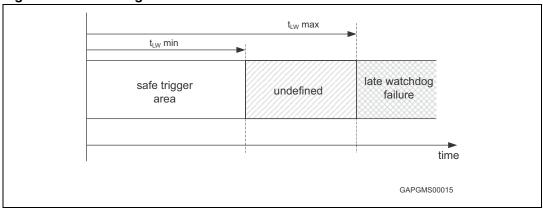


Figure 10. Watchdog timing

Figure 11. Watchdog late and safe window



8.7 Current monitor output CM

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 15. Current monitor output CM

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
	Current monitor output ratio: I _{CM} /I _{OUT1,5,9} and 8 (low on-resistance)	$0~V \leq V_{CM} \leq V_{CC} - 1~V$		1/10000		
^I CM r	I _{CM} /I _{OUT2,3,4,6,7} and 8 (high on- resistance)			1/2000		

Symbol Test condition Min. Max. Unit **Parameter** Typ. 0 V \leq V_{CM} \leq V_{CC} - 1 V; $I_{OUTmin} = 500 \text{ mA};$ Current monitor accuracy $I_{OUT9max} = 5.9 A;$ accl_{CMOUT1,5,9} and 8 (low on-res.) $I_{OUT1,5max} = 2.9 A;$ 4% + 1% 8% + 2% $I_{OUT8max} = 1.3 A$ I_{CM acc} FS⁽¹⁾ FS⁽¹⁾ 0 V \leq $V_{CM} \leq$ V_{CC} - 1 V; $I_{OUT.min} = 100 \text{ mA};$ accl_{CMOUT2,3,4,6,7} and 8 (high on-res.) $I_{OUT2,3,4,6,7max} = 0.6 A;$ $I_{OUTXmax} = 0.3 A$

Table 15. Current monitor output CM (continued)

8.8 Charge pump output CP

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 16. Charge pump output CP

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
	V _{CP} Charge pump output voltage	$V_S = 8 \text{ V}, I_{CP} = -60 \mu\text{A}$	V _S + 6		V _S + 13	٧
V_{CP}		V_S = 10 V, I_{CP} = -80 μA	V _S + 8		V _S + 13	>
		$V_S \geq 12$ V, I_{CP} = -100 μA	V _S + 10		V _S + 13	٧
I _{CP}	Charge pump output current	$V_{CP} = V_S + 10 \text{ V},$ $V_S = 13.5 \text{ V}$	95	150	300	μΑ

8.9 Outputs OUT1 – OUT9, ECV, ECFD

8.9.1 On-resistance

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 17. On-resistance

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
R _{ON OUT1,5}	IOn-registance to supply or GND	$V_S = 13.5 \text{ V}, T_{amb} = +25 \text{ °C}$ $I_{OUT1,5} = \pm 1.5 \text{ A}$		300	400	mΩ
		V _S = 13.5 V, T _{amb} = +125 °C I _{OUT1,5} = ±1.5 A		450	600	mΩ
R _{ON OUT2,3,4} On-resistance to supply or G	On registance to quantum or CND	V _S = 13.5 V, T _{amb} = +25 °C I _{OUT2,3,4} = ±0.4 A		1600	2200	mΩ
		$V_S = 13.5 \text{ V}, T_{amb} = +125 \text{ °C}$ $I_{OUT2,3,4} = \pm 0.4 \text{ A}$		2500	3400	mΩ

^{1.} FS(full scale) = I_{OUTmax} * I_{CM r}

Table 17. On-resistance (continued)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
D	On recistoring to supply	V _S = 13.5 V, T _{amb} = +25 °C I _{OUT6,7} = -0.4 A		1600	2200	mΩ
R _{ON OUT6,7}	On-resistance to supply	V _S = 13.5 V, T _{amb} = +125 °C I _{OUT6,7} = -0.4 A		2500	3400	mΩ
	On-resistance to supply in low	$V_S = 13.5 \text{ V}, T_{amb} = +25 \text{ °C}$ $I_{OUT8} = -3.0 \text{ A}$		500	700	mΩ
Bou outs	resistance mode	$V_S = 13.5 \text{ V}, T_{amb} = +125 \text{ °C}$ $I_{OUT8} = -3.0 \text{ A}$		700	950	mΩ
R _{ON OUT8}	On-resistance to supply in high resistance mode	$V_S = 13.5 \text{ V}, T_{amb} = +25 \text{ °C}$ $I_{OUT8} = -0.8 \text{ A}$		1800	2400	mΩ
		$V_S = 13.5 \text{ V}, T_{amb} = +125 \text{ °C}$ $I_{OUT8} = -0.8 \text{ A}$		2500	3400	mΩ
R	On-resistance to supply	$V_S = 13.5 \text{ V}, T_{amb} = +25 \text{ °C}$ $I_{OUT9} = -3.0 \text{ A}$		90	130	mΩ
R _{ON OUT9}		$V_S = 13.5 \text{ V}, T_{amb} = +125 \text{ °C}$ $I_{OUT9} = -3.0 \text{ A}$		130	180	mΩ
R	On-resistance to GND	$V_S = 13.5 \text{ V}, T_{amb} = +25 \text{ °C}$ $I_{OUTECV,ECFD} = +0.4 \text{ A}$		1600	2200	mΩ
R _{ON ECV,ECFD}		V _S = 13.5 V, T _{amb} = +125 °C I _{OUTECV,ECFD} = +0.4 A		2500	3400	mΩ
1.	Switched-off output current	V _{OUT} = 0 V, standby mode	-5	-2		μΑ
I_{QLH}	high-side drivers of OUT1-9	V _{OUT} = 0 V, active mode	-10.5	-7		μA
	Switched-off output current	V _{OUT} = V _S , standby mode		80	120	μΑ
	low-side drivers of OUT1-5	V _{OUT} = V _S , active mode	-10	-7		μΑ
	Switched-off output current	V _{OUT} = V _S , standby mode	-15		15	μΑ
I _{QLL}	low-side drivers of ECV	V _{OUT} = V _S , active mode	-10	-7		μΑ
	Switched-off output current	V _{OUT} = 4V, standby mode		80	120	μΑ
	low-side drivers of ECFD	V _{OUT} = 4V, active mode	-10	-7		μΑ

8.9.2 Switching times

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 18. Switching times

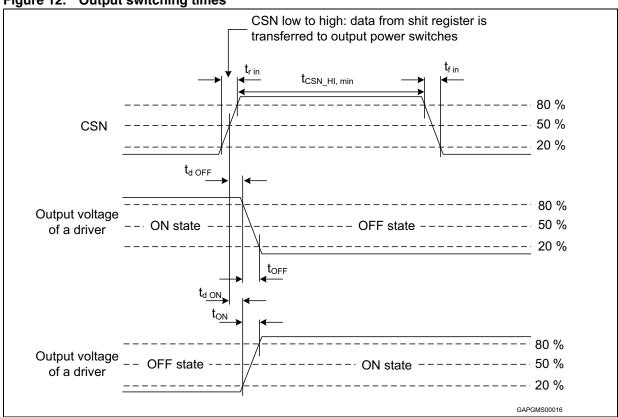
Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _{d ON H}	Output delay time high-side driver on	$V_S = 13.5 \text{ V},$ corresponding low-side driver is not active $^{(1)(2)(3)}$	20	40	80	μs
t _{d OFF H}	Output delay time high-side driver off	V _S = 13.5 V ⁽¹⁾⁽²⁾⁽³⁾	45	150	300	μs

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Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _d ON L	Output delay time low-side driver on	V _S = 13.5 V, corresponding low-side driver is not active ⁽¹⁾⁽²⁾⁽³⁾	15	30	70	μs
t _d OFF L	Output delay time low-side driver off	V _S = 13.5 V ⁽¹⁾⁽²⁾⁽³⁾	80	150	300	μs
t _{d HL}	Cross current protection time	t _{cc ONLS_OFFHS} - t _{d OFF H} ⁽⁴⁾		200	410	116
t _{d LH}	O1033 Current protection time	t _{cc ONHS_OFFLS} - t _{d OFF L} ⁽⁴⁾			410	μs
dVou±/dt	Slew rate of OUTx	$V_c = 13.5 \text{ V}^{(1)(2)(3)}$	0.1	0.2	0.6	V/us

Table 18. Switching times (continued)

- 1. $R_{load} = 16$ at OUT1,5 and OUT8 in low on-resistance mode.
- 2. $R_{load} = 4$ at OUT9.
- 3. R_{load} = 64 at OUT2,3,4,6,7, ECV, ECFD and OUT8 in high on-resistance mode.
- 4. t_{CC} is the switch-on delay time if complement in half bridge has to switch off.

Figure 12. Output switching times



8.9.3 Current monitoring

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 19. Current monitoring

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
II _{OC1} I, II _{OC5} I	Overcurrent threshold to supply or		3		5	Α
_{OC2} , _{OC3} , _{OC4}	GND	$V_S = 13.5 \text{ V}$, sink and source	0.75		1.25	Α
II _{OC6} I, II _{OC7} I	Overcurrent threshold to supply	V _S = 13.5 V, source	0.75		1.25	Α
H 1	Overcurrent threshold to supply in low on-resistance mode	V _S = 13.5 V, source	1.5		2.5	Α
II _{OC8} I	Overcurrent threshold to supply in high on-resistance mode	V _S = 13.5 V, source	0.35		0.65	Α
II _{OC9} I	Overcurrent threshold to supply	V _S = 13.5 V, source	6		10	Α
II _{OCECV} I, II _{OCECFD} I	Output current limitation to GND	V _S = 13.5 V, sink	0.72		1.25	Α
t _{FOC}	Filter time of overcurrent signal	Duration of overcurrent condition to set the status bit	10	55	100	μs
f _{rec0}	Recovery frequency for OC recovery duty cycle bit = 0		1		4	kHz
f _{rec1}	Recovery frequency for OC recovery duty cycle bit = 1		2		6	kHz
II _{OLD1} I, II _{OLD5} I	Linday august threahald to august or		9	30	80	mA
II _{OLD2} I, II _{OLD3} I, II _{OLD4} I	Under-current threshold to supply or GND	$V_S = 13.5 \text{ V}$, sink and source	10	20	30	mA
II _{OLD6} I, II _{OLD7} I	Under-current threshold to supply		10	20	30	mA
11 1	Under-current threshold to supply in low on-resistance mode	V _S = 13.5 V, source	15	40	60	mA
II _{OLD8} I	Under-current threshold to supply in high on-resistance mode		5	10	15	mA
II _{OLD9} I	Under-current threshold to supply		30	150	300	mA
II _{OLDECV} I, II _{OLDECFD} I	Under-current threshold to GND	V _S = 13.5 V, sink	10	20	30	mA
t _{FOL}	Filter time of under-current signal	Duration of under-current condition to set the status bit	0.5	2.0	3.0	ms

8.9.4 Electrochrome control

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 20. Electrochrome control

Symbol	Paramete	er	Test condition	Min.	Тур.	Max.	Unit
M	Maximum FC as at	est velte es	ECVL = '1' (1)	1.4		1.6	V
V _{CTRLmax}	Maximum EC-conti	oi voitage	ECVL = '0' (1)	1.12		1.28	V
DNL _{ECV}	Differential non line	arity		-1		1	LSB ⁽²⁾
ldV _{ECV} l	Voltage deviation b target and ECV	etween	$dV_{ECV} = V_{target}^{(3)} - V_{ECV}$, $II_{ECDR}I < 1 \mu A$	-5% - 1LSB ⁽²⁾		+5% + 1LSB ⁽²⁾	mV
dV _{ECVnr}	between target	below it	$dV_{ECV} = V_{target}^{(3)} - V_{ECV}$ Toggle bit5 = 1 Status reg. 3		120		mV
dV _{ECVhi}	and ECV sets flag if V _{ECV} is	above it	dV _{ECV} = V _{target} ⁽³⁾ - V _{ECV} Toggle bit4 = 1 Status reg. 3		-120		mV
t _{FECVNR}	ECVNR filter time				32		μs
t _{FECO}	ECVO filter time				32		μs
V _{ECDRminHIGH}	Output voltage rang	70	I _{ECDR} = -10 μA	4.1		5.5	V
V _{ECDRmaxLOW}	Output voltage rang	y e	I _{ECDR} = 10 μA	0		0.7	V
			$V_{target}^{(3)} > V_{ECV} + 500 \text{ mV},$ $V_{ECDR} = 3.5 \text{ V}$	-100		-10	μΑ
I _{ECDR}	Current into ECDR		$\begin{aligned} & V_{target}^{(3)} < V_{ECV} 500 \text{ mV}, \\ & V_{ECDR} = 1.0 \text{ V}; V_{target} = 0 \text{ V}, \\ & V_{ECV} = 0.5 \text{ V} \end{aligned}$	10		100	μΑ
R _{ecdrdis}	Pull down resistand in fast discharge m while EC-mode is o	ode and	V _{ECDR} = 0.7 V, ECON = '1', EC<5:0> = 0 or ECON = '0'			10	kΩ
DNL _{ECFD}	Differential non line	arity		-1		1	LSB ⁽²⁾
IdV _{ECFD} I	Voltage deviation b target and ECFD	etween	$ \frac{\text{dV}_{\text{ECFD}} = \text{V}_{\text{target}}^{(3)} - \text{V}_{\text{ECFD}}}{\text{I}_{\text{ECFD}} = 100 \ \mu\text{A}} $	-5% - 1LSB ⁽²⁾		+5% + 1LSB ⁽²⁾	mV
dV _{ECFDnr} ⁽⁴⁾	Difference voltage between target	below it	dV _{ECFD} = V _{target} ⁽³⁾ - V _{ECFD} toggle status bit ECVNR = '1'		120		mV
dV _{ECFDhi}	and ECFD sets flag if V _{ECFD} is	above it	dV _{ECFD} = V _{target} ⁽³⁾ - V _{ECFD} toggle status bit ECVO = '1'		-120		mV

^{1.} Bit ECVL = '1' or '0': ECV voltage, where I_{ECDR} can change sign.

^{2. 1} LSB (Least Significant Bit) = 23.8 mV.

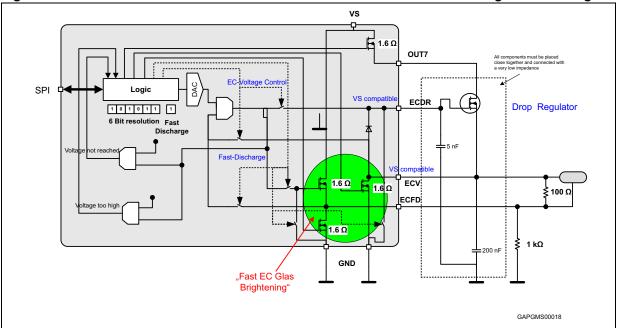
^{3.} V_{target} is set by bits EC <5:0> and bit ECVL; tested for each individual bit.

Not tested since pulling pin ECFD to a low voltage against the internal source follower may lead to an overcurrent at pin ECFDHS or thermal shutdown.

1.6 Ω OUT7 All components must be placed close together and connected with a very low impedance SPI Logic **ECDR** Drop Regulator 1 0 1 0 1 1 1 6 Bit resolution Fast Discharge Fast-Discharge EC-Mirror ECV 1.6 Ω 1.6 Ω **ECFD** 1.6 Ω GND "Fast EC Glas Brightening" GAPGMS00017

Figure 13. Electrochrome mirror driver with mirror referenced to ground





8.9.5 INH/PWM3 input

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 8 V \leq V_S \leq 16 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 21. INH/PWM3 input

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
I _{INHth}	Wake-up activate threshold current		30	75	120	μA
I _{INHPd}	INH pull down current	V _{INH} = 13.5 V	30	70	120	μΑ
I _{INHhys}	Wake-up current hysteresis			10	20	μΑ
t _{WU}	Minimum time for wake-up		50	64	77	μs

8.10 LIN

Compatible to LIN 2.1 for baud rates up to 20 kBit/s

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 7 V \leq V_S \leq 18 V; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 22. LIN

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
LIN transmit	data input: pin TXD		•			
V _{TXDLOW}	Input voltage dominant level	Active mode			0.3 V _{CC}	٧
V _{TXDHIGH}	Input voltage recessive level	Active mode	0.7 V _{CC}			٧
V _{TXDHYS}	V _{TXDHIGH} - V _{TXDLOW}	Active mode	500			mV
R _{TXDPU}	TXD pull up resistor	Active mode, $V_S = 13.5 \text{ V}$, $0 < V_{CSN} < 0.7 \text{ V}_{CC}$	50	100	150	k
LIN receive	data output: pin RXD		·			
V _{RXDLOW}	Output voltage dominant level	Active mode, I _{RXD} = 2 mA			0.3 V _{CC}	٧
V _{RXDHIGH}	Output voltage recessive level	Active mode, I _{RXD} = 2 mA	0.7 V _{CC}			٧
LIN transmit	ter and receiver: pin LI	N				
V_{THdom}	Receiver threshold voltage recessive to dominant state		0.4 V _S	0.45 V _S	0.5 V _S	V
V _{THrec}	Receiver threshold voltage dominant to recessive state		0.5 V _S	0.55 V _S	0.6 V _S	V

Table 22. LIN (continued)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V_{THhys}	Receiver threshold hysteresis: V _{THrec} - V _{THdom}		0.07 V _S	0.1 V _S	0.175 V _S	V
V _{THcnt}	Receiver tolerance center value: (V _{THrec} + V _{THdom}) / 2		0.475 V _S	0.5 V _S	0.525 V _S	V
V_THwkup	Receiver wake-up rising threshold voltage		1.0	1.5	2	٧
$V_{THwkdwn}$	Receiver wake-up falling threshold voltage		V _S - 3.5	V _S - 2.5	V _S - 1.5	٧
t _{LINBUS}	Dominant time for wake-up via bus	Sleep mode edge: recessive- dominant		64*T _{OSC}		μs
I _{BUS_LIM}	Current limitation in dominant state	V _{TXD} = 0 V, V _{LIN} = V _{SMAX} = 18 V	40	100	180	mA
I _{BUS_PAS_dom}	Input leakage current at the receiver (incl. pull up resistor)	V _{TXD} = 5 V, V _{LIN} = 0 V, V _S = 13.5 V	-1			mA
I _{BUS_PAS_rec}	Transmitter input current in recessive state	$V_{TXD} = 5 \text{ V, } 8 \text{ V} \le V_{LIN,} \text{ V}_{S} \le 18 \text{ V,} \\ V_{LIN} \ge V_{S}$			20	μΑ
I _{BUS_NO_GND}	Transceiver input current if loss of GND at device	GND = V _S , 0 V < V _{LIN} < 18 V, V _S = 13.5 V	-1		1	mA
I _{BUS_NO_BAT}	Input current if loss of V _{BAT} at Device	V _S = GND, 0 V < V _{LIN} < 18 V			100	μΑ
V _{LINdom}	LIN voltage level in dominant state	Active mode; V _{TXD} = 0 V; I _{LIN} = 40 mA			1.3	٧
V _{LINrec}	LIN voltage level in recessive state	Active mode; $V_{TXD} = 5 \text{ V}$; $I_{LIN} = 10 \mu A$	0.8 V _S		V _S	٧
R _{LINup}	LIN output pull up resistor	V _{TXD} = 5 V; V _{LIN} = 0 V	20	40	60	kΩ
LIN transceiv	er timing					
^t RXDpd	Receiver propagation delay time	Active Mode; $t_{RXDpd} = max(t_{RXDpdr}, t_{RXDpdf});$ $t_{RXpdf} = t(0.5 \ V_{RXD}) - t(0.45 \ V_{LIN})$ $t_{RXpdr} = t(0.5 \ V_{RXD}) - t(0.55 \ V_{LIN})$ $V_S = 13.5 \ V; \ C_{RXD} = 20 \ pF;$ $R_{BUS} = 1 \ k\Omega, \ C_{BUS} = 1 \ nF;$			6	μs
t _{RXDpd_sym}	Symmetry of receiver propagation delay time (rising vs. falling edge)	$t_{RXDpd_sym} = t_{RXDpdr} - t_{RXDpdf}$	-2		2	μs

Table 22. LIN (continued)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
D1	Duty cycle 1	$\begin{split} TH_{Rec}(\text{max}) &= 0.744 ^* \text{V}_{\text{S}}; \\ TH_{Dom}(\text{max}) &= 0.581 ^* \text{V}_{\text{S}}; \\ \text{V}_{\text{S}} &= 7 \text{ to } 18 \text{ V}, t_{\text{bit}} = 50 \mu \text{s}; \\ \text{D1} &= t_{\text{BUS}_{rec}}(\text{min}) / (2 ^* t_{\text{bit}}); \\ R_{\text{BUS}} &= 1 \text{k} \Omega, C_{\text{BUS}} = 1 \text{nF}; \\ R_{\text{BUS}} &= 660 \Omega, C_{\text{BUS}} = 6.8 \text{nF}; \\ R_{\text{BUS}} &= 500 \Omega, C_{\text{BUS}} = 10 \text{nF} \end{split}$	0.396			
D2	Duty cycle 2	$\begin{split} &TH_{Rec}(min) = 0.422^*V_S; \\ &TH_{Dom}(min) = 0.284^*V_S; \\ &V_S = 7.6 \text{ to } 18 \text{ V, bit} = 50 \mu\text{S;} \\ &D2 = t_{BUS_rec}(max)/(2^*t_{bit}); \\ &R_{BUS} = 1 k\Omega, C_{BUS} = 1 n\text{F;} \\ &R_{BUS} = 660 \Omega, C_{BUS} = 6.8 n\text{F;} \\ &R_{BUS} = 500 \Omega, C_{BUS} = 10 n\text{F} \end{split}$			0.581	
D3	Duty cycle 3	$\begin{split} &TH_{Rec}(max) = 0.778^*V_S; \\ &TH_{Dom}(max) = 0.616^*V_S; \\ &V_S = 7 \text{ to } 18V, t_{bit} = 96\mu\text{s}, \\ &D3 = t_{BUS_rec}(min)/(2^*t_{bit}) \\ &R_{BUS} = 1 \text{ k}\Omega, C_{BUS} = 1 \text{ nF}; \\ &R_{BUS} = 660 \ \Omega, C_{BUS} = 6.8 \text{ nF}; \\ &R_{BUS} = 500 \ \Omega, C_{BUS} = 10 \text{ nF} \end{split}$	0.417			
D4	Duty cycle 4	$\begin{split} TH_{Rec}(\text{min}) &= 0.389^* V_S; \\ TH_{Dom}(\text{min}) &= 0.251^* V_S; \\ V_S &= 7.6 \text{ to } 18 V, t_{bit} = 96 \mu s; \\ D4 &= t_{BUS_rec}(\text{max})/(2^* t_{bit}) \\ R_{BUS} &= 1 \text{ k} \Omega, C_{BUS} = 1 \text{ nF}; \\ R_{BUS} &= 660 \ \Omega, C_{BUS} = 6.8 \text{ nF}; \\ R_{BUS} &= 500 \ \Omega, C_{BUS} = 10 \text{ nF} \end{split}$			0.590	
t _{dom(TXD)}	TXD dominant time- out			12		ms
t _{dom(LIN)}	BUS dominant time- out			12		ms
t _{rec(LIN)}	BUS recessive time- out			40		μs
LIN Flash m	ode					
SR _{FLASH}	LIN slew rate falling edge in Flash mode	Active mode; LIN slew rate (80% to 20% V_S); $V_S = 13.5 V$, $R_{BUS} = 150 \Omega$, $C_{BUS} = 1 nF$		13		V/µs

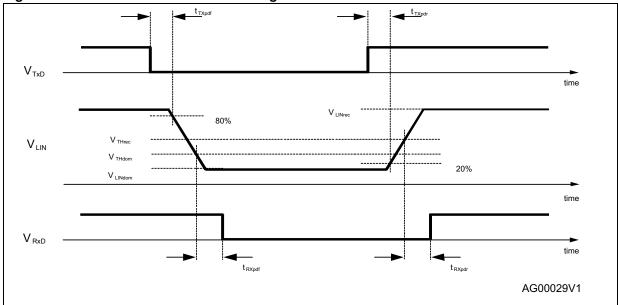


Figure 15. LIN transmit and receive timing

8.11 SPI and PWM inputs

8.11.1 DC characteristics

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq V $_{S} \leq$ 18 V; all outputs open; T $_{amb}$ = -40 °C...125 °C, unless otherwise specified.

Table 23. DC characteristics

iabic 20.	DO Characteristics					
Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
Inputs: CSN,	CLK, DI, PWM1, PWM2, PWM	ЛЗ				
V _{IL}	Input voltage low-level	V _S = 13.5 V			0.3 V _{CC}	٧
V _{IH}	Input voltage high-level	V _S = 13.5 V	0.7 V _{CC}			V
V _{IHYS}	Input hysteresis	V _S = 13.5 V	500			mV
R _{CSN in}	CSN pull up resistor	V _S = 13.5 V, 0 < V _{CSN} < 0.7 V _{CC}	30	120	250	kΩ
R _{CLK in}	CLK pull down resistor	V _S = 13.5 V, V _{CLK} = 1.5 V	30	60	150	kΩ
R _{DI in}	DI pull down resistor	V _S = 13.5 V, V _{DI} = 1.5 V	30	60	150	kΩ
R _{PWM1 in}	PWM1 pull down resistor	V _S = 13.5 V, V _{PWM1} = 1.5 V	30	60	150	kΩ
R _{PWM2 in}	PWM2 pull down resistor	V _S = 13.5 V, V _{PWM2} = 1.5 V	30	60	150	kΩ
	PWM3	See Section 8.9.5	: INH/PWN	13 inpu	rt	
Output: DO		·				
V _{OL}	Output voltage low-level	$I_{OL} = 5 \text{ mA}, V_{S} = 13.5 \text{ V}$			0.3 V _{CC}	٧
V _{OH}	Output voltage high-level	I _{OH} = -5mA, V _S = 13.5 V	0.7 V _{CC}			٧
	1	1				

8.11.2 AC characteristics

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq V_S \leq 18 V; all outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 24. AC characteristics

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
C _{OUT} ⁽¹⁾	Output capacitance (DO)		_	_	10	pF
C _{IN} ⁽¹⁾	Input capacitance (DI, CSN, CLK, PWM1, PWM2, PWM3)		_		10	pF

^{1.} Value of input capacity is not measured in production test. Parameter guaranteed by design.

8.11.3 Dynamic characteristics

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq V_S \leq 18 V; all outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified.

For definition of the parameters please see *Figure 16* and *Figure 17*.

Table 25. Dynamic characteristics

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _{CSNQVL}	DO enable from 3-state to low-level	C_{DO} = 100 pF, I_{DO} = 1 mA, pull up load to V_{CC} , V_{S} = 13.5 V		100	250	ns
t _{CSNQVH}	DO enable from 3-state to high-level	C_{DO} = 100 pF, I_{DO} = -1 mA, pull down load to GND, V_{S} = 13.5 V		100	250	ns
t _{CSNQTL}	DO disable from low-level to 3-state	C_{DO} = 100 pF, I_{DO} = 4 mA, pull up load to V_{CC} , V_{S} = 13.5 V		380	450	ns
t _{CSNQTH}	DO disable from high-level to 3-state	C_{DO} = 100 pF, I_{DO} = -4 mA, pull down load to GND, V_{S} = 13.5 V		380	450	ns
+	CLIV falling until DO valid	$V_{DO} < 0.3 V_{CC} \text{ or } V_{DO} > 0.7 V_{CC}$ $C_{DO} = 5 \text{ pF}, V_{S} = 13.5 \text{ V}$				ns
^t CLKQV	CLK falling until DO valid	$V_{DO} < 0.3 V_{CC} \text{ or } V_{DO} > 0.7 V_{CC}$ $C_{DO} = 100 \text{ pF}, V_{S} = 13.5 \text{ V}$		50	250	ns
t _{SCSN}	CSN setup time, CSN low before rising edge of CLK	V _S = 13.5 V	400			ns
t _{SDI}	DI setup time, DI stable before rising edge of CLK	V _S = 13.5 V	200			ns
t _{HDI}	DI hold time, DI stable after rising edge of CLK	V _S = 13.5 V	200			ns
t _{HCLK}	minimum CLK high time	V _S = 13.5 V	115			ns
t _{LCLK}	minimum CLK low time	V _S = 13.5 V	115			ns
t _{HCSN}	minimum CSN high time	V _S = 13.5 V	4			μs
t _{SCLK}	CLK setup time before CSN rising	V _S = 13.5 V	400			ns

Table 25. Dynamic characteristics (continued)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _{r DO}	DO rise time	$C_{DO} = 100 \text{ pF}, V_S = 13.5 \text{ V}$		80	140	ns
t _{f DO}	DO fall time	$C_{DO} = 100 \text{ pF}, V_S = 13.5 \text{ V}$		50	100	ns
I	rise time of input signal DI, CLK, CSN	V _S = 13.5 V			100	ns
t _{f in}	fall time of input signal DI, CLK, CSN	V _S = 13.5 V			100	ns

Figure 16. SPI timing parameters

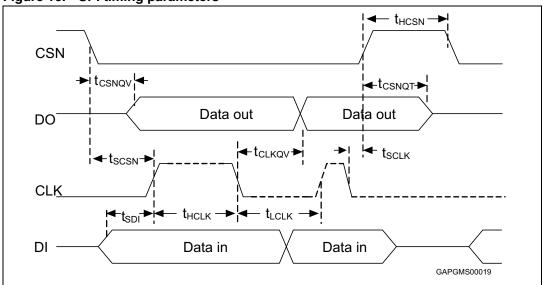
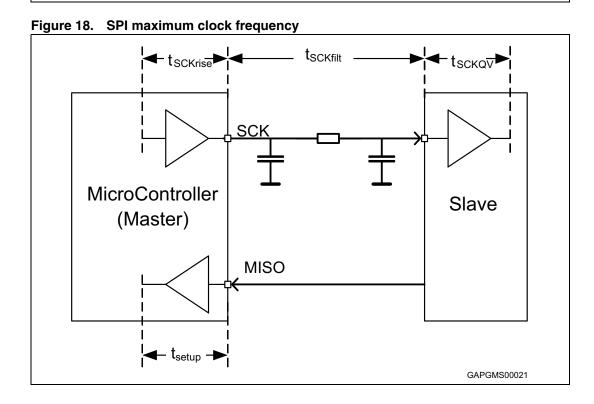


Figure 17. SPI input and output timing parameters $t_{\text{r}\,\text{DO}}$ ----- 0.8 V_{CC} DO (low to high) ----- 0.2 V_{CC} t_{fDO} $0.8 V_{CC}$ DO (high to low) ----- 0.2 V_{CC}

→ t_{f in} DI -- 0.8 V_{CC} CLK **CSN** - 0.2 V_{CC} GAPGMS00020



The maximum SPI clock frequency can be calculated as follows (see Figure 18):

 $t_{CLKQV}(total) = t_{CLKrise}(\mu C) + t_{CLKfilt}(PCB) + t_{CLKQV}(slave) + t_{setup}(\mu C)$

 $f_{CLK}(max) < \frac{1}{2} x t_{CLKQV}(total)$

Example:

 $t_{CLKQV} = 25 \text{ ns} + 100 \text{ ns} + 250 \text{ ns} + 25 \text{ ns} = 400 \text{ ns}$

 $f_{CLK}(max) < 1.25 \text{ MHz}$

8.12 Input PWM2 for Flash mode

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 6 V \leq V_S \leq 18 V; all outputs open; T_{amb} = -40 °C...125 °C, unless otherwise specified.

Table 26. Input PWM2 for Flash mode

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V _{flashL}	Input low-level (PWM2 falling) ⁽¹⁾	V _S = 13.5 V	6.1	7.25	8.4	٧
V _{flashH}	Input high-level (PWM2 rising)	$V_S = 13.5 \text{ V}, V_{BAT\text{-standby}}$ mode, V_{CC} switches on	7.4	8.4	9.4	٧
V _{flashHYS}	Input voltage hysteresis ⁽¹⁾	V _S = 13.5 V	0.6	0.8	1.0	٧

^{1.} Parameter guaranteed by design.

9 SPI control and status registers

9.1 Functional description of the SPI

For a general description of the SPI please refer to chapter Serial peripheral interface (ST SPI standard).

9.1.1 SPI communication flow

At the beginning of each communication the master can read the contents of the <SPI-frame-ID> register (ROM address 3Eh) of the slave device. This 8 bit register indicates the SPI frame length (24 bit) and the availability of additional features.

Each communication frame consists of a command byte which is followed by 2 data bytes.

The data returned on DO within the same frame always starts with the <Global Status Byte>. It provides general status information about the device. It is followed by 2 data bytes (i.e. "in-frame-response").

For write cycles the <Global Status Byte> is followed by the previous content of the addressed register.

9.1.2 Command byte

Table 27. Command byte

	Command byte					Data byte 1							Data byte 2											
Bit	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Name	OC1	OC0	A5	A4	АЗ	A2	A1	A0	D15	D14	D13	D12	D11	D10	D9	D8	D7	D6	D5	D4	D3	D2	D1	D0

OCx: operation code

Ax: address Dx: data bit

Each communication frame starts with a command byte. It consists of an operating code which specifies the type of operation (<Read>, <Write>, <Read and Clear>, <Read Device Information>) and a 6 bit address. If less than 6 bits are required, the remaining bits are unused but are reserved.

9.1.3 Operation code definition

Table 28. Operation code definition

OC1	OC0	Meaning
0	0	<write mode=""></write>
0	1	<read mode=""></read>
1	0	<read and="" clear="" mode=""></read>
1	1	<read device="" information=""></read>

The <Write Mode> and <Read Mode> operations allow access to the RAM of the device.

A <Read and Clear Mode> operation is used to read a status register and subsequently clear its content.

The <Read Device Information> allows access to the ROM area which contains device related information such as <ID-Header>, <Product Code>, <Silicon Version> and <SPI-frame-ID>.

9.1.4 Global status byte

Table 29. Global status byte

Bit				Global s	tatus byte)							
ы	7	6	5	4	3	2	1	0					
Name	GL_ER	CO_ER	NRECE	TSD	TW_OL	UV_OV_OC	V _{CC} _FAIL	PASSIVE					
Reset	1	0	0	0	0	0	0	0					
GL_ER	combination of register, TW_GL_ER is ref	ts 0-6 are allof all failure OL is not us lected via thong as CSN	events of the sed as an inp e DO pin wh is low. This o	e device. If out to this b ile CSN is	the TW_C oit. held low a	g. This flag is on the second of the second	et in the conf nal is availab	iguration le. The flag					
CO_ER	is set.	of clock pul		•		not 24, the fram		and this bit					
NRECE = NOT (C_RESET OR CO_ER)	After power of NRECE is als stuck-at-1 at When NREC	Chip reset (C_RESET) = Registers have been set to default. After power on NRECE is '0' and is set to '1' by a valid SPI communication. NRECE is also '0' if there was a communication error or if there was a reset due to stuck-at-0 or stuck-at-1 at the SPIDI input. When NRECE is active ('0'), the gate drivers are switched off (resistive path to source). The gate drivers can only be activated after NRECE has been reset with an SPI command.											
TSD		resistive pat	h to source)	. The TSD	bit has to	drivers and the be cleared thro							
TW_OL	Thermal warr	ning OR ope	n-load.										
UV_OV_OC	Under voltage	e OR overvo	ltage OR ov	ercurrent									
V _{CC_FAIL}	V _{CC} fail												
PASSIVE Device in passive mode. This bit is set if the device enters passive mode (due to watchdog failure, V _{CC} under voltage, thermal shutdown TSD2 or SPI data in stuck at 0 or 1) The bit is reset when the micro sends the first correct SPI frame after entering passive mode.													



9.1.5 Address mapping

Table 30. RAM memory map

Address	Name	Access	Content
01h	Control register 1	Read/write	Bridge control, watchdog trigger
02h	Control register 2	Read/write	High/low-side control, EC control
03h	Control register 3	Read/write	Bridge recovery mode, bridge PWM mode, LIN
04h	Control register 4	Read/write	HS recovery and PWM mode, LS recovery and PWM mode, current monitor
11h	Status register 1	Read/clear	Overcurrent diagnosis
12h	Status register 2	Read/clear	Open-load diagnosis
13h	Status register 3	Read/clear	WD status, supply voltage and EC diagnosis,
14h	Status register 4	Read/clear	LIN diagnosis, thermal status
3Fh	Configuration register	Read/write	

Table 31. ROM memory map

Address	Name	Access	Content
00h	ID Header	Read only	4300h (ASSP ST_SPI)
01h	Version	Read only	0000h (engineering sample)
02h	Product code 1	Read only	4800h (dec. 72)
03h	Product code 2	Read only	4800h (ASCII 'H')
3Eh	SPI frame ID	Read only	4200h (watchdog available, 24 bit ST-SPI)

9.1.6 Control registers

Table 32. Control registers 1

	Control register 1 (01h)															
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0
Name	OUT5 HS	OUT5 LS	OUT4 HS	OUT4 LS	OUT3 HS	OUT3 LS	OUT2 HS	OUT2 LS	OUT1 HS	OUT1 LS	NINT EN	RST LEV	ICMP	Stby Sel	Go Stby	WD Trig

Table 33. Control registers 1, bits

Bit name	Comment
OUT5HS	
OUT5LS	
OUT4HS	
OUT4LS	If a bit is set, the selected output driver is switched on. If the corresponding PWM enable bit is set
OUT3HS	also, the driver is activated only if the associated PWM input signal is high.
OUT3LS	The outputs of OUT1 – OUT5 are half bridges. If the bits of the HS and LS drivers of the same half bridge are set, both drivers are deactivated and the output is set to high impedance.
OUT2HS	bridge are set, both drivers are deactivated and the output is set to high impedance.
OUT2LS	
OUT1HS	
OUT1LS	
NINTEN	Enable NINT output 0: RXD output has only RXD functionality 1: RXD output can work also as NINT output
RSTLEV	Select V _{CC} reset level 0: 4.7 V 1: 3.5 V
I _{CMP}	Monitor the I_{CC} current consumption during $V_{CC\text{-standby}}$ mode 0: watchdog disabled only if $I_{CC} < I_{CMP}$ 1: watchdog disabled
STBYSEL	Standby select 0: V _{BAT-standby} 1: V _{CC-standby} This bit is a one-shot bit, it is read always 0
GOSTBY	1: execute standby mode This bit is a one-shot bit, it is read always 0
WDTRIG	Watchdog trigger This bit has to be toggled regularly if the watchdog is active. The watchdog can be triggered either by this bit or by bit 0 of the configuration register.

Table 34. Control registers 2

		Control register 2 (02h)														
Bit	15 14 13 12 11 10 9 8 7 6 5 4 3 2 1											1	0			
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Name	reserved	ECFDLS	ECVLS	OUT9	OUT8HS2	OUT8HS1	OUT7	OUT6	ECND	EC5	EC4	EC3	EC2	EC1	EC0	ECON

Table 35. Control registers 2, bits

Bit name	Comment
reserved	Reserved bit, has always to be written to 0 and reads always 0
ECFDLS	1: switch on the ECFD LS driver 0: switch off the ECFD LS driver
ECVLS	1: switch on the ECV LS driver 0: switch off the ECV LS driver If the ECVPWM1 bit (CR4/Bit4) is also set, then the ECV output is controlled by the PWM1 input
OUT9	1: switch on the OUT9 HS driver 0: switch off the OUT9 HS driver If the OUT9PWM1 bit (CR4/Bit11) is also set, then the OUT9 output is controlled by the PWM1 input
OUT8HS2	11: switch off the OUT8 HS driver
OUT8HS1	10: switch on the OUT8 HS driver (high current mode) 01: switch on the OUT8 HS driver (low current mode) 00: switch off the OUT8 HS driver If the OUT8PWM3 bit (CR4/Bit10) is also set, then the OUT8 output is controlled by the PWM3 input
OUT7	1: switch on the OUT7 HS driver 0: switch off the OUT7 HS driver If the OUT7PWM1 bit (CR4/Bit9) is also set, then the OUT7 output is controlled by the PWM1 input This bit is disabled if ECON = 1. In this case OUT7 is switched on permanently.
OUT6	1: switch on the OUT6 HS driver 0: switch off the OUT6 HS driver If the OUT6PWM2 bit (CR4/Bit8) is also set, then the OUT6 output is controlled by the PWM2 input
ECND	EC negative discharge: 0: EC negative discharge off 1: EC negative discharge on
EC5	
EC4	
EC3	Reference value for difference voltage amplifier at pin ECV, binary coded. The full scale value is set in
EC2	ECVL (CR3/Bit5). If all EC bits are set to zero, the reference value is 0V.
EC1	
EC0	
ECON	1: EC control enabled 0: EC control disabled If the EC control is enabled, the output OUT7 is switched on permanently.

Table 36. Control register 3

		Control register 3 (03h)														
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0
Name	reserved	OCR Freq	OVUVR	OUT5 OR	OUT4 OR	OUT3 OR	OUT2 OR	OUT1 OR	LIN Flash	LIN TXD Tout	ECVL	OUT5 PWM1	OUT4 PWM1	OUT3 PWM1	OUT2 PWM1	OUT1 PWM1

Table 37. Control register 3, bits

Bit name	Comment
reserved	Reserved bit, has always to be written to 0 and reads always 0
OCRFREQ	OCR frequency: This bit defines the overcurrent recovery frequency of a driver in overcurrent recovery mode 0: 1.7 kHz 1: 3 kHz
OVUVR	Overvoltage/undervoltage recovery: 1: clear status register to enable the outputs after an overvoltage/undervoltage event 0: outputs are enabled automatically after an overvoltage/undervoltage event
OUT5OR	
OUT4OR	Overcurrent recovery enable:
OUT3OR	1: the output is automatically reactivated after a delay time with programmable duty cycle (CR3/Bit14)
OUT2OR	0: clear status register to enable the output after an overcurrent event
OUT1OR	
LINFLASH	LIN flash mode: 0: 20 kbit/s 1: 100 kbit/s
LINTXDTout	Dominant TxD time-out for the LIN interface: 1: enable the dominant TXD time-out for the LIN interface 0: disable the dominant TXD time-out for the LIN interface
ECVL	EC voltage limit: 0: max EC voltage = 1.2V 1: max EC voltage = 1.5V
OUT5PWM1	
OUT4PWM1	
OUT3PWM1	If the PWM enable bit is set and the output is enabled, the output is switched on only if the PWM1 input is high, and switched off if the PWM1 input is low.
OUT2PWM1	
OUT1PWM1	

Table 38. Control register 4

		Control register 4 (04h)														
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Name	OUT9 OR	OUT8 OR	OUT7 OR	OUT6 OR	OUT9 PWM1	OUT8 PWM3	OUT7 PWM1	OUT6 PWM2	reserved	ECV OR	reserved	ECV PWM1	СМЗ	CM2	CM1	СМО

Table 39. Control register 4, bits

Bit name	Comment
OUT9OR	Ougraphicant recovery enables
OUT8OR	Overcurrent recovery enable: 1: the output is automatically reactivated after a delay time with programmable duty cycle
OUT7OR	(CR3/Bit14) 0: clear status register to enable the output after an overcurrent event
OUT6OR	o. clear status register to eriable the output after an overcurrent event
OUT9PWM1	
OUT8PWM3	If the PWM1/2/3 enable bit is set and the output is enabled, the output is switched on only if the PWM1/2/3 input is high, and switched off if the PWM1/2/3 input is low.
OUT7PWM1	OUT8 is controlled by PWM3, OUT7 is controlled by PWM1 and OUT6 is controlled by PWM2.
OUT6PWM2	
reserved	Reserved bit, has always to be written to 0 and reads always 0
ECVOR	Overcurrent recovery enable: 1: the output is automatically reactivated after a delay time with programmable duty cycle (CR3/Bit14) 0: clear status register to enable the output after an overcurrent event
reserved	Reserved bit, has always to be written to 0 and reads always 0
ECVPWM1	If the PWM1 enable bit is set and the output is enabled, the output is switched on only if the PWM1 input is high, and switched off if the PWM1 input is low.

Table 39. Control register 4, bits (continued)

Bit name					Comment	
		monitor ent imag		selected	high-side output is multiple	exed to the CM output (see table below).
	СМЗ	CM2	CM1	СМО	Current image of	
	0	0	0	0	CM deactivated	
	0	0	0	1	CM HS1 active	
	0	0	1	0	CM HS2 active	
	0	0	1	1	CM HS3 active	
	0	1	0	0	CM HS4 active	
CM3	0	1	0	1	CM HS5 active	
CM2 CM1	0	1	1	0	CM HS6 active	
CM0	0	1	1	1	CM HS7 active	
	1	0	0	0	CM HS8 active	
	1	0	0	1	CM HS9 active	
	1	0	1	0	reserved	
	1	0	1	1	reserved	
	1	1	0	0	reserved	
	1	1	0	1	reserved	
	1	1	1	0	reserved	
	1	1	1	1	reserved	

Table 40. Configuration register

		Configuration register (3Fh)											
Bit	7	6	5	4	3	2	1	0					
Reset state	0	0	0	0	0	0	0	0					
Name		ECV ECFD OUT7 OLMASK	OUT1HS OLMASK	OUT1LS OLMASK	TW_OL MASK			WD TRIG					

Table 41. Configuration register, bits

Bit name	Comment
	The bits 15 to 8 of the configuration register have to be written to 0, and read always 0
ECV ECFD OUT7 OLMASK	Mask the ECV, ECFD (HS and LS) and OUT7 open-load diagnostics bits (status reg. 2, bits 11, 14, 15): an open-load event is not considered in the open-load bit (TW_OL) of the global status register
OUT1HS OLMASK	Mask the OUTHS1 open-load diagnostic bit (status reg. 1/bit 1): an open-load event (under-current status bit of OUT1HS) is not considered in open-load bit (TW_OL) of the global status register.
OUT1LS OLMASK	Mask the OUTLS1 open-load diagnostic bit (status reg. 1/bit 0): an open-load event (under-current status bit of OUT1LS) is not considered in open-load bit (TW_OL) of the global status register.
TW_OL MASK	Mask the TW_OL bit in global status byte: a temperature warning or open-load event is not considered in the "global error flag"
WDTRIG	Trigger the watchdog. This bit has to be toggled regularly if the watchdog is active. The watchdog can be triggered either by this bit or by bit 0 of the Control Register 1.

9.1.7 Status registers

Table 42. Status register 1

		Status register 1 (11h)														
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Name	ECFDLS	ECV LS	OUT 9HS	OUT 8HS	OUT 7HS	OUT 6HS	OUT5 HS	OUT5 LS	OUT4 HS	OUT4 LS	OUT3 HS	OUT3 LS	OUT2 HC	OUT2 LS	OUT1 HS	OUT1 LS

Table 43. Status register 1, bits

Bit name	Comment
ECFDLSOC	
ECVLSOC	
OUT9HSOC	
OUT8HSOC	
OUT7HSOC	
OUT6HSOC	
OUT5HSOC	Overcurrent diagnosis: In case of an overcurrent event the corresponding status bit is set and the output driver is disabled.
OUT5LSOC	If the overcurrent recovery enable bit is set, the output is automatically reactivated after a delay time
OUT4HSOC	resulting in a PWM modulated current with a programmable duty cycle.
OUT4LSOC	If the overcurrent recovery bit is not set, the microcontroller has to clear the overcurrent bit to reactivate the output driver.
OUT3HSOC	
OUT3LSOC	
OUT2HSOC	
OUT2LSOC	
OUT1HSOC	
OUT1LSOC	

Table 44. Status register 2

		Status register 2 (12h)														
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Name	ECFD LS	ECV LS	OUT9	OUT8	OUT7	OUT6	OUT5 HS	OUT5 LS	OUT4 HS	OUT4 LS	OUT3 HS	OUT3 LS	OUT2 HS	OUT2 LS	OUT1 HS	OUT1 LS

Table 45. Status register 2, bits

Bit name	Comment
ECFDLSOL	
ECVLSOL	
OUT9OL	
OUT8OL	
OUT7OL	The open-load detection monitors the load current in each activated output stage. If the load current is below the under current detection threshold for at least $t_{dOL} = 2$ ms, the corresponding open-load
OUT6OL	bit is set. Due to the mechanical / electrical inertia of typical loads a short activation of the outputs
OUT5HSOL	(e.g. 3 ms) can be used to test the open-load status without changing the mechanical / electrical state of the loads.
OUT5LSOL	The open-load detection of OUT1 HS and OUT1 LS can be masked by the configuration register
OUT4HSOL	(Bit 4/5).
OUT4LSOL	The open-load detection of ECFDLS, ECVLS and OUT7 can be masked by the configuration register (Bit 6).
OUT3HSOL	
OUT3LSOL	
OUT2HSOL	
OUT2LSOL	
OUT1HSOL	Maskable by the configuration register:
OUT1LSOL	an open-load event is not considered in open-load bit (TW_OL) of global status register.

Table 46. Status register 3

							Stat	us regi	ster 3 (1	3h)						
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Name	LIN perm dom	LIN TXD dom	LIN prem rec	VCC fail	UV	OV	WD timer state	WD timer state	ECFD HSOC	ECFD HSOL	ECV NR	ECVO		TSD2	TSD1	TW

Table 47. Status register 3, bits

Bit name	Comment								
LIN perm dom	If the bus state is dominant (low) for more than 12 ms a permanent dominant status is detected. The status bit is set.								
LIN TXD dom	If TXD is in don	If TXD is in dominant state (low) for more than 12 ms, the transmitter is disabled and this bit is set.							
LIN perm rec	If TXD changes to dominant (low) state but RXD signal does not follow within 40 μs, the transmitter is disabled and this bit is set.								
V _{CCFail}	V_{CCFail} : $V_{CC} < 2 \text{ V for more than 2 } \mu \text{s}$								
UV	V _S undervoltag	e detected		an over/under voltage event is detected	ed, the outputs are				
OV	V _S overvoltage detected			disabled and one of these bits is set. If the OVUVR bit is 0, the outputs are enabled automatically after an over/under voltage event and the UV/OV bit is reset. If the OVUVR bit is 1, the outputs are enabled after clearing the UV/OV bit by SPI command (read and clear operation)					
WDTIM1	WDTIM1 Watchdog state: Display which part of the total WD time (100 ms) has been elapsed:								
	WDTIM1 WDTIM0			Elapsed time					
WDTIM0	0	0		< 1/3 of the total WD time					
VVDTIIVIO	0	1		< 2/3 of the total WD time					
	1	1		< 3/3 of the total WD time					
ECFDHSOC	Overcurrent diagnosis: In case of an overcurrent event on ECFDHS the status bit is set and the output driver is disabled.								
ECFDHSOL	The open-load detection monitors the load current in the ECFDHS. If the load current is below the under current detection threshold for at least $t_{dOL} = 2$ ms, the open-load bit is set.								
ECVNR	ECV voltage not reached Two comparators monitor the voltage at pin ECV in ele								
ECVO	ECV voltage too high			mode. If this voltage is below / above the programmed target, these bits signal the difference after at least 32 µs. The bits are not latched and may toggle after at least 32 µs, if the ECV voltage has not yet reached the target.					
LCVO			has	s not yet reached the target.					
TSD2	Thermal shutdo	own 2 (> 160 °C		s not yet reached the target.					
	Thermal shutdo	·	C)	s not yet reached the target.					

All bits except the WDTIM1, WDTIM0, ECVNR and ECVO bits can be reset by a read and clear operation on SR4.

Table 48. Status register 4

		Status register 4 (14h)														
Bit	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Reset state	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0
Name	WD fail	WD fail	WD fail	WD fail	Forced SleepWD	Forced SleepTSD	Dev State	Dev State		VCC Restart	VCC Restart	VCC Restart	NOT RDY	SPI Wake	LIN Wake	INH Wake

Table 49. Status register 4, bits

Bit name		Comment								
WDFAIL3						Those hits are not clearable, are				
WDFAIL2	NI	r of watcho	log fails			These bits are not clearable, are cleared with a proper watchdog trigge				
WDFAIL1	INI	i oi waterit	log ialis			or if the chip is sent to V _{BAT-standby} by the watchdog.				
WDFAIL0						the watchdog.				
Forced sleep WD		nis bit is se the watch		o has been set to V _{BAT-sta}	_{ndby} mode	These bits are latched until a "read and clear" access on SR4.				
Forced sleep TSD	Tł by	nis bit is se / a therma	t if the chip I shutdowr	ว has been set to V _{BAT-sta} า	_{ndby} mode					
DEVSTATE1	Si	gnal devic	e state:							
		DEV STATE1	DEV STATE2	State						
		0	0	Active						
		0	1	$V_{CC ext{-standby}}$						
		1	0	V _{BAT} standby or POR		These bits are latched until a "read and				
DEVSTATE0		1	1		clear" access on SR 4.					
	wi Th m op cu	ith a read a nerefore, the ode or flas perations a	and clear one first reach mode reached a reach	dated with any state trans command on status regis d operation after entering eads the last device state d and clear operation read fter power-on reset, the o	ter 4. g active . Read ds the					
VCCRestart2										
VCCRestart1	Nı	r of TSD re	estart trials	3		These bits are latched until a "read and clear access" on SR 4.				
VCCRestart0										
NOTRDY	st	andby to a	ctive mod	et for 200µs after switchi e. It is cleared automatica ut drivers are disabled.		This bit is not clearable, it is cleared automatically.				

Table 49. Status register 4, bits (continued)

Bit name	Comment	
SPIWake	Indicates wake-up from V _{CC-standby} mode via SPI	
LINWake	Indicates wake-up from V _{CC-standby} mode via LIN	These bits are latched until a "read and clear" access on SR4.
INHWake	Indicates wake-up from V _{CC-standby} mode via INH	

10 Package and packaging information

10.1 ECOPACK®

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

10.2 PowerSSO-36 package information

Figure 19. PowerSSO-36 package dimensions

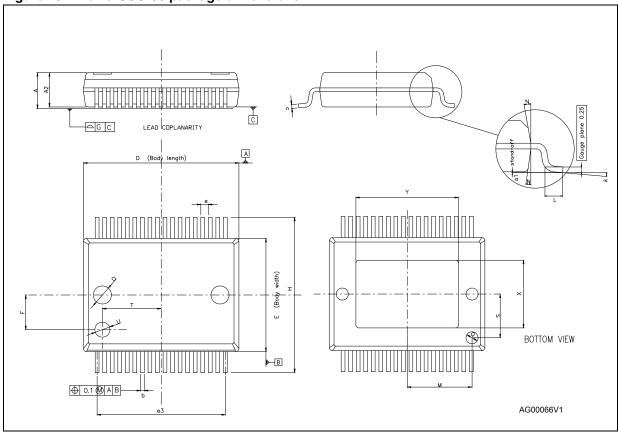


Table 50. PowerSSO-36 mechanical data

Oh al	Millimeters									
Symbol	Min.	Тур.	Max.							
А	2.15	-	2.45							
A2	2.15	-	2.35							
a1	0	-	0.10							
b	0.18	-	0.36							
С	0.23	-	0.32							
D ¹	10.10	-	10.50							
E ¹	7.4	-	7.6							
е	-	0.5	-							
e3	-	8.5	-							
F	-	2.3	-							
G	-	-	0.1							
G1	-	-	0.06							
Н	10.1	-	10.5							
h	-	-	0.4							
k	0°	-	8°							
L	0.55	-	0.85							
М	-	4.3	-							
N	-	-	10°							
0	-	1.2	-							
Q	-	0.8	-							
S	-	2.9	-							
Т	-	3.65	-							
U	-	1	-							
Х	4.3	-	5.2							
Y	6.9	-	7.5							

Note: "D" and "E" do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.15 mm per side.

L99MM70XP Revision history

11 Revision history

Table 51. Document revision history

Date	Revision	Changes
04-Jan-2012	1	Initial release.
19-Sep-2013	2	Updated Disclaimer.

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